TPS38-Q1 車載用、ワイド V_{IN}、65V デュアル・チャネル過電圧 / 低電圧 (OV/UV) 検出器、プログラマブル・センス / リセット機能付き

1 特長

- 以下の結果で AEC-Q100 認定済み:
  - デバイス温度グレード 1:–40℃～+125℃の動作時周囲温度範囲 T_A
  - デバイス HBM ESD 分類レベル 2
  - デバイス CDM ESD 分類レベル C7B
- 広い電源電圧範囲:2.7V～65V
- 機能安全への対応を予定
  - 機能安全システムの設計に役立つ資料を利用可能
- 65V 定格の SENSE および RESET ピン
- 低静止電流:1μA (標準値)
- 電圧スレッショルドを柔軟にかつ幅広く選択可能 表 10-1
  - 2.7V～36V (誤差 1.5% 以下)
  - 800mV オプション (誤差 1% 以下)
- ヒステリシス内蔵 (V_{HYS})
  - パーセンテージ・オプション:2%～13% (1% 刻み)
  - 固定オプション:V_{TH} < 8V = 0.5V、1V、1.5V、2V、2.5V
- リセット時間遅延をプログラム可能
  - 10nF = 12.8ms、10μF = 12.8s
- 検出時間遅延をプログラム可能
  - 10nF = 1.28ms、10μF = 1.28s
- マニュアル・リセット ($\overline{MR}$) 機能
- 出力トポロジ:
  - チャネル 1:オープン・ドレインまたはプッシュプル
  - チャネル 2:オープン・ドレイン

2 アプリケーション

- テレマティクス制御ユニット
- 緊急通話システム
- オーディオ・アンプ
- ヘッド・ユニットおよびクラスタ
- センサ・フュージョンおよびカメラ
- ボディ・コントロール・モジュール

3 概要

TPS38-Q1 は、I_{DD} = 1μA、精度 1%、検出時間が 10μs と短い 65V 入力電圧検出器です。
このデバイスは 12V/24V 車載用バッテリ・システムに直接接続し、過電圧 (OV) または低電圧 (UV) 状態を継続的に監視できます。また、抵抗デバイダを内蔵しているため、ソリューション全体のサイズを最小化できます。
コールド・クランク、スタート / ストップ、車の各種バッテリ電圧過渡の影響を受けないように、各種ヒステリシス電圧を選択できます。SENSE ピンに組み込まれたヒステリシスは、電源電圧レール監視中のリセット信号の誤検出を防止します。

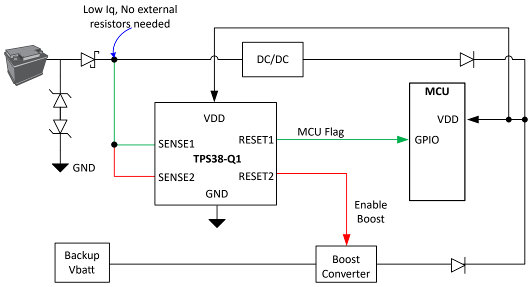
VDD ピンと SENSE ピンが独立しているため、信頼性が高い車載用システムが求める冗長性を実現できます。また、SENSE は VDD よりも高い電圧と低い電圧を監視できます。SENSE ピンは高インピーダンス入力であるため、任意で外付け抵抗を使用できます。CTSx および CTRx ピンを使うことで、RESET 信号の立ち上がり / 立ち下がりエッジの遅延を調整できます。また、CTSx は、監視対象の電圧レールの電圧グリッチを無視するデバウンシング機能として機能します。CTRx は、システムを強制的にリセットするためのマニュアル・リセット ($\overline{MR}$) としても動作します。

TPS38-Q1 は WSON または SOT-23 パッケージで供給されます。WSON パッケージはウェッタブル・フランクを採用しているため、自動光学検査 (AOI) と低解像度 X 線検査を容易に実施できます。IEC60664 のガイドラインに基づいて VDD と GND との間の沿面距離を増やすため、中央パッドはどこにも接続されていません。

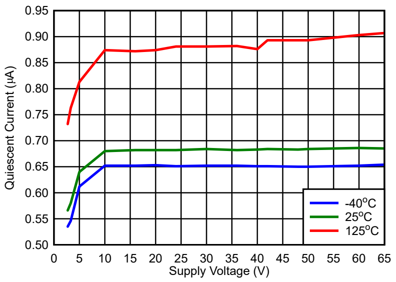
製品情報

部品番号	パッケージ[1]	本体サイズ (公称)
TPS38-Q1	WSON (10) (DSK)	2.5mm × 2.5mm
TPS38-Q1	SOT-23 (14) (DYY)	4.1mm × 1.9mm

(1) パッケージの詳細については、このデータシートの末尾の外形図を参照してください。



代表的なアプリケーション回路



I_{DD} と V_{DD} との代表的な関係

Table of Contents

4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

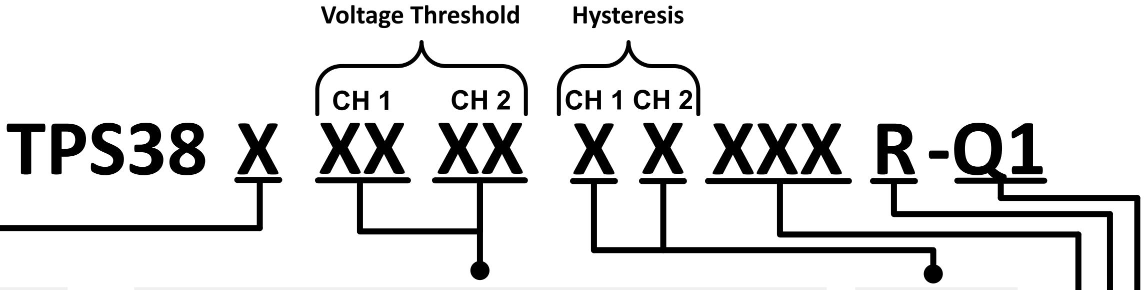
Changes from Revision D (July 2023) to Revision E (August 2023)	Page
• Added Hysteris accuracy diagram	11
• Updated the typical characteristic curves	14

Changes from Revision C (December 2021) to Revision D (July 2023)	Page
• データシート全体にわたって、DYY パッケージの製品プレビューを削除	1

Changes from Revision B (September 2021) to Revision C (December 2021)	Page
• 「事前情報」から「量産データ」のリリースに変更	1

5 Device Comparison

Contact TI sales representatives or consult TI's E2E forum for details and availability; minimum order quantities may apply.



Topology		
Suffix	CH1	CH2
A	UV OD L	UV OD L
B	UV PP L	UV OD L
D	UV PP L	UV OD H
E	UV PP H	UV OD H
F	UV PP H	UV OD L
G	UV OD H	UV OD H
H	UV OD H	UV OD L
J	OV OD L	OV OD L

M	OV PP L	OV OD L
N	OV PP L	OV OD H
O	OV PP H	OV OD H
P	OV PP H	OV OD L

Threshold Voltage									
100mV steps				400mV steps		500mV steps		1V steps	
Suffix	VIT	Suffix	VIT	Suffix	VIT	Suffix	VIT	Suffix	VIT
01	800mV	70	7.0V	A0	10.4V	D0	20.5V	F0	31.0V
27	2.7V	71	7.1V	A1	10.8V	D1	21.0V	F1	32.0V
28	2.8V	72	7.2V	A2	11.2V	D2	21.5V	F2	33.0V
29	2.9V	73	7.3V	A3	11.6V	D3	22.0V	F3	34.0V
30	3.0V	74	7.4V	A4	12.0V	D4	22.5V	F4	35.0V
31	3.1V	75	7.5V	A5	12.4V	D5	23.0V	F5	36.0V
32	3.2V	76	7.6V	A6	12.8V	D6	23.5V		
33	3.3V	77	7.7V	A7	13.2V	D7	24.0V		
34	3.4V	78	7.8V	A8	13.6V	D8	24.5V		
35	3.5V	79	7.9V	A9	14.0V	D9	25.0V		
36	3.6V	80	8.0V	B0	14.4V	E0	25.5V		
37	3.7V	81	8.1V	B1	14.8V	E1	26.0V		
38	3.8V	82	8.2V	B2	15.2V	E2	26.5V		
39	3.9V	83	8.3V	B3	15.6V	E3	27.0V		
40	4.0V	84	8.4V	B4	16.0V	E4	27.5V		
41	4.1V	85	8.5V	B5	16.4V	E5	28.0V		
42	4.2V	86	8.6V	B6	16.8V	E6	28.5V		
43	4.3V	87	8.7V	B7	17.2V	E7	29.0V		
44	4.4V	88	8.8V	B8	17.6V	E8	29.5V		
45	4.5V	89	8.9V	B9	18.0V	E9	30.0V		
46	4.6V	90	9.0V	C0	18.4V				
47	4.7V	91	9.1V	C1	18.8V				
48	4.8V	92	9.2V	C2	19.2V				
49	4.9V	93	9.3V	C3	19.6V				
50	5.0V	94	9.4V	C4	20.0V				
51	5.1V	95	9.5V						
52	5.2V	96	9.6V						
53	5.3V	97	9.7V						
54	5.4V	98	9.8V						
55	5.5V	99	9.9V						
56	5.6V	00	10.0V						
57	5.7V								
58	5.8V								
59	5.9V								
60	6.0V								
61	6.1V								
62	6.2V								
63	6.3V								
64	6.4V								
65	6.5V								
66	6.6V								
67	6.7V								
68	6.8V								
69	6.9V								

Hysteresis	
Suffix	CH1
2	2%
3	3%
4	4%
5	5%
6	6%
7	7%
8	8%
9	9%
A	10%
B	11%
C	12%
D	13%
E	0.5V
F	1V
G	1.5V
H	2V
I	2.5V

Package	
Suffix	Name
DSK	WSON
DYY	SOT-23

Reel	
Suffix	Name
R	Large

Rating	
Suffix	Name
Q1	AUTO
	INDUSTRIAL

図 5-1. Device Nomenclature

1. Sense logic: OV = overvoltage; UV = undervoltage
2. Reset topology: PP = Push-Pull; OD = Open-Drain
3. Reset logic: L = Active-Low; H = Active-High
4. A to I hysteresis options are only available for 2.7 V to 8 V threshold options

6 Pin Configuration and Functions

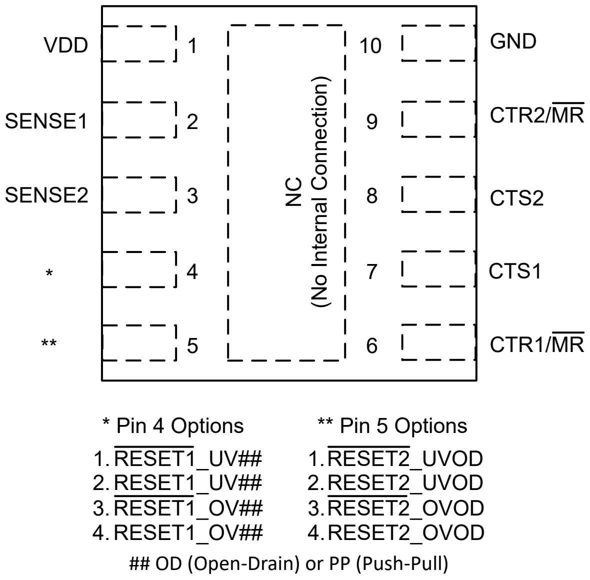


図 6-1. DSK Package,
10-Pin WSON,
TPS38-Q1 (Top View)

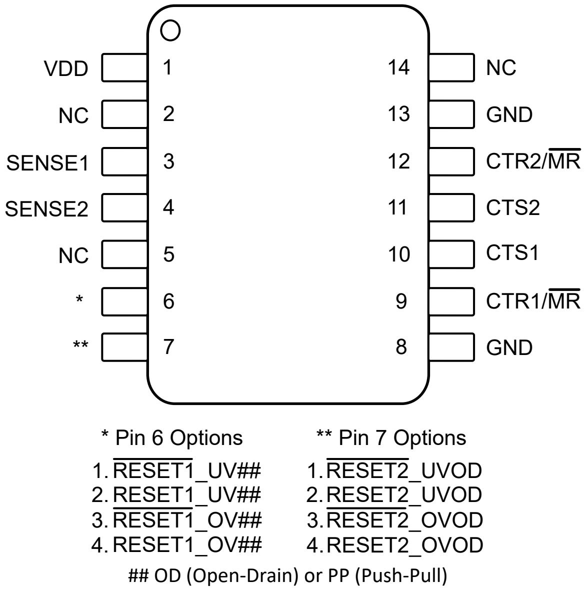


図 6-2. DYY Package,
14-Pin SOT-23,
TPS38-Q1 (Top View)

表 6-1. Pin Functions

PIN NAME	WSON (DSK)	SOT23 (DYY)	I/O	DESCRIPTION
	PIN NUM.	PIN NUM.		
VDD	1	1	I	**Input Supply Voltage:** Bypass with a 0.1 µF capacitor to GND.
SENSE1	2	3	I	This pin is connected to the voltage that will be monitored for fixed variants or to a resistor divider for the adjustable variant. Depending on the SENSE1 sensing configuration, when the voltage on SENSE1 pin detects an undervoltage (UV) or an overvoltage (OV) fault, $\overline{\text{RESET1}}$/RESET1 asserts after the sense time delay, set by CTS1. When the voltage on the SENSE1 pin transitions back to an unfaulty UV or OV state, $\overline{\text{RESET1}}$/RESET1 deasserts after the reset time delay, set by CTR1. For noisy applications, placing a 10 nF to 100 nF ceramic capacitor close to this pin may be needed for optimum performance.
SENSE2	3	4	I	This pin is connected to the voltage that will be monitored for fixed variants or to a resistor divider for the adjustable variant. Depending on the SENSE2 sensing configuration, when the voltage on SENSE2 pin detects an undervoltage (UV) or an overvoltage (OV) fault, $\overline{\text{RESET2}}$/RESET2 asserts after the sense time delay, set by CTS2. When the voltage on the SENSE2 pin transitions back to an unfaulty UV or OV state, $\overline{\text{RESET2}}$/RESET2 deasserts after the reset time delay, set by CTR2. For noisy applications, placing a 10 nF to 100 nF ceramic capacitor close to this pin may be needed for optimum performance.
$\overline{\text{RESET1}}$/ RESET1	4	6	O	**Output Reset Signal For Channel 1:** See セクション 5 for output topology options. $\overline{\text{RESET1}}$/RESET1 asserts when SENSE1 detects an undervoltage or overvoltage fault condition. $\overline{\text{RESET1}}$/RESET1 remains asserted for the reset time delay period after SENSE1 transitions out of an UV or OV fault condition. For active low open-drain reset output, an external pullup resistor is required. Do not place external pullup resistors on push-pull outputs. Reset output signal for: **SENSE1** Sensing Topology: **Undervoltage (UV) or Overvoltage (OV)** Output topology: **Open Drain or Push Pull, Active Low or Active High**
$\overline{\text{RESET2}}$/ RESET2	5	7	O	**Output Reset Signal For Channel 2:** See セクション 5 for output topology options. $\overline{\text{RESET2}}$/RESET2 asserts when SENSE2 detects an undervoltage or overvoltage fault condition. $\overline{\text{RESET2}}$/RESET2 remains asserted for the reset time delay period after SENSE2 transitions out of an UV or OV fault condition. For active low open-drain reset output, an external pullup resistor is required. Reset output signal for: **SENSE2** Sensing Topology: **Undervoltage (UV) or Overvoltage (OV)** Output topology: **Open Drain, Active Low or Active High**
CTR1/ $\overline{\text{MR}}$	6	9	-	**Channel 1 RESET Time Delay:** User-programmable reset time delay for $\overline{\text{RESET1}}$/RESET1. Connect an external capacitor for adjustable time delay or leave the pin floating for the shortest delay. **Manual Reset:** If this pin is driven low, the $\overline{\text{RESET1}}$/RESET1 output will reset and become asserted. The pin can be left floating or be connected to a capacitor. This pin should not be driven high.
CTR2/ $\overline{\text{MR}}$	9	12	-	**Channel 2 RESET Time Delay:** User-programmable reset time delay for $\overline{\text{RESET2}}$/RESET2. Connect an external capacitor for adjustable time delay or leave the pin floating for the shortest delay. **Manual Reset:** If this pin is driven low, the $\overline{\text{RESET2}}$/RESET2 output will reset and become asserted. The pin can be left floating or be connected to a capacitor. This pin should not be driven high.
GND	10	8, 13	-	**Ground.** All GND pins must be electrically connected to the board ground.
NC	PAD	2, 5, 14	-	The PAD for the **DSK** package is not internally connected, the PAD can be connected to GND or be left floating. For the **DYY** package, NC stands for "No Connect". The pins are to be left floating.
CTS1	7	10	O	**Channel 1 SENSE Time Delay:** Capacitor programmable sense delay: CTS1 pin offers a user-adjustable sense delay time when asserting a reset condition. Connecting this pin to a ground-referenced capacitor sets the $\overline{\text{RESET1}}$/RESET1 delay time to assert.
CTS2	8	11	O	**Channel 2 SENSE Time Delay:** Capacitor programmable sense delay: CTS2 pin offers a user-adjustable sense delay time when asserting a reset condition. Connecting this pin to a ground-referenced capacitor sets the $\overline{\text{RESET2}}$/RESET2 delay time to assert.

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range, unless otherwise noted (1)

		MIN	MAX	UNIT
Voltage	VDD, V_{SENSE1},V_{SENSE2}, V_{RESET1}, V_{RESET2}, $V_{\overline{RESET1}}$, $V_{\overline{RESET2}}$	–0.3	70	V
Voltage	V_{CTS1}, V_{CTS2}, V_{CTR1}, V_{CTR2}	–0.3	6	V
Current	I_{RESET1}, I_{RESET2}, $I_{\overline{RESET1}}$, $I_{\overline{RESET2}}$		10	mA
Temperature (2)	Operating junction temperature, T_J	–40	150	°C
Temperature (2)	Operating Ambient temperature, T_A	–40	150	°C
Temperature (2)	Storage, T_{stg}	–65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) As a result of the low dissipated power in this device, it is assumed that $T_J = T_A$.

7.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per AEC Q100-002 (1)	±2000	V
		Charged device model (CDM), per AEC Q100-011	±750	

(1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
Voltage	V_{DD}	2.7		65	V
Voltage	V_{SENSE1},V_{SENSE2}, V_{RESET1}, V_{RESET2}, $V_{\overline{RESET1}}$, $V_{\overline{RESET2}}$	0		65	V
Voltage	V_{CTS1}, V_{CTS2}, V_{CTR1}, V_{CTR2}	0		5.5	V
Current	I_{RESET1}, I_{RESET2}, $I_{\overline{RESET1}}$, $I_{\overline{RESET2}}$	0		±5	mA
T_J	Junction temperature (free air temperature)	–40		125	°C

7.4 Thermal Information

THERMAL METRIC (1)		TPS38-Q1		UNIT
		DSK	DYY	
		10-PIN	14-PIN	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	87.4	131.5	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	76.3	61.6	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	54.2	56.6	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	4.8	3.4	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	54.2	56.5	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	34.8	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

7.5 Electrical Characteristics

At $V_{DD(MIN)} \le V_{DD} \le V_{DD\ (MAX)}$, CTR1/$\overline{\text{MR}}$ = CTR2/$\overline{\text{MR}}$ = CTS1 = CTS2 = open, output reset pull-up resistor R_{PU} = 10 kΩ, voltage V_{PU} = 5.5 V, and load C_{LOAD} = 10 pF. The operating free-air temperature range T_A = – 40°C to 125°C, unless otherwise noted. Typical values are at T_A = 25°C and VDD = 16 V and V_{IT} = 6.5 V (V_{IT} refers to V_{ITN} or V_{ITP}).

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
VDD						
V_{DD}	Supply Voltage		2.7		65	V
UVLO (1)	Undervoltage Lockout	V_{DD} Falling below $V_{DD\ (MIN)}$			2.7	V
V_{POR}	Power on Reset Voltage (2) $\overline{\text{RESET}}$, Active Low (Open-Drain, Push-Pull)	$V_{OL(MAX)}$ = 300 mV $I_{OUT\ (Sink)}$ = 15 µA			1.4	V
V_{POR}	Power on Reset Voltage (2) RESET, Active High (Push-Pull)	$V_{OH(MIN)}$ = 0.8 x V_{DD} $I_{OUT\ (Source)}$ = 15 µA			1.4	V
I_{DD}	Supply current into VDD pin	V_{IT} = 800 mV $V_{DD\ (MIN)} \le V_{DD} \le V_{DD\ (MAX)}$		1	2.6	µA
		V_{IT} = 2.7 V to 36 V $V_{DD\ (MIN)} \le V_{DD} \le V_{DD\ (MAX)}$		1	2	µA
SENSE (Input)						
I_{SENSE}	Input current (SENSE1, SENSE2)	V_{IT} = 800 mV			100	nA
I_{SENSE}	Input current (SENSE1, SENSE2)	V_{IT} < 10 V			0.8	µA
I_{SENSE}	Input current (SENSE1, SENSE2)	10 V < V_{IT} < 26 V			1.2	µA
I_{SENSE}	Input current (SENSE1, SENSE2)	V_{IT} > 26 V			2	µA
V_{ITN}	Input Threshold Negative (Undervoltage)	V_{IT} = 2.7 V to 36 V	-1.5		1.5	%
		V_{IT} = 800 mV (3)	0.792	0.800	0.808	V
V_{ITP}	Input Threshold Positive (Overvoltage)	V_{IT} = 2.7 V to 36 V	-1.5		1.5	%
		V_{IT} = 800 mV (3)	0.792	0.800	0.808	V
V_{HYS}	Hysteresis Accuracy (4)	V_{IT} = 0.8 V and 2.7 V to 36 V V_{HYS} Range = 2% to 13% (1% step)	-1.5		1.5	%
		V_{IT} = 2.7 V to 8 V V_{HYS} = 0.5 V, 1 V, 1.5 V, 2 V, 2.5 V (V_{ITP} - $V_{HYS)}$ ≥ 2.4 V, OV Only	-1.5		1.5	%
RESET (Output)						
$I_{lkg(OD)}$	Open-Drain leakage (RESET1, RESET2)	V_{RESET} = 5.5 V $V_{ITN} < V_{SENSE} < V_{ITP}$			300	nA
		V_{RESET} = 65 V $V_{ITN} < V_{SENSE} < V_{ITP}$			300	nA
V_{OL} (5)	Low level output voltage	2.7 V ≤ VDD ≤ 65 V I_{RESET} = 5 mA			300	mV
V_{OH_DO}	High level output voltage dropout (V_{DD} - V_{OH} = V_{OH_DO}) (Push-Pull only)	2.7 V ≤ VDD ≤ 65 V I_{RESET} = 500 uA			100	mV
V_{OH} (5)	High level output voltage (Push-Pull only)	2.7 V ≤ VDD ≤ 65 V I_{RESET} = 5 mA	$0.8V_{DD}$			V

7.5 Electrical Characteristics (continued)

At $V_{DD(MIN)} \leq V_{DD} \leq V_{DD\ (MAX)}$, CTR1/$\overline{MR}$ = CTR2/$\overline{MR}$ = CTS1 = CTS2 = open, output reset pull-up resistor R_{PU} = 10 kΩ, voltage V_{PU} = 5.5 V, and load C_{LOAD} = 10 pF. The operating free-air temperature range T_A = – 40°C to 125°C, unless otherwise noted. Typical values are at T_A = 25°C and VDD = 16 V and V_{IT} = 6.5 V (V_{IT} refers to V_{ITN} or V_{ITP}).

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Capacitor Timing (CTS, CTR)						
R_{CTR}	Internal resistance (CTR1 / $\overline{MR}$, CTR2 / $\overline{MR}$)		877	1000	1147	Kohms
R_{CTS}	Internal resistance ($C_{TS1,}$ C_{TS2})		88	100	122	Kohms
Manual Reset ($\overline{MR}$)						
$V_{\overline{MR}\_IH}$	CTR1 / $\overline{MR}$ and CTR2 / $\overline{MR}$ pin logic high input	VDD = 2.7 V	2200			mV
$V_{\overline{MR}\_IH}$	CTR1 / $\overline{MR}$ and CTR2 / $\overline{MR}$ pin logic high input	VDD = 65 V	2500			mV
$V_{\overline{MR}\_IL}$	CTR1 / $\overline{MR}$ and CTR2 / $\overline{MR}$ pin logic low input	VDD = 2.7 V			1300	mV
$V_{\overline{MR}\_IL}$	CTR1 / $\overline{MR}$ and CTR2 / $\overline{MR}$ pin logic low input	VDD = 65 V			1300	mV

(1) When V_{DD} voltage falls below UVLO, reset is asserted for Output 1 and Output 2. V_{DD} slew rate ≤ 100 mV / µs
(2) V_{POR} is the minimum V_{DD} voltage for a controlled output state. Below VPOR, the output cannot be determined. V_{DD} dv/dt ≤ 100mV/µs
(3) For adjustable voltage guidelines and resistor selection refer to **Adjustable Voltage Thresholds** in **Application and Implementation section**
(4) Hysteresis is with respect to V_{ITP} and V_{ITN} voltage threshold. V_{ITP} has negative hysteresis and V_{ITN} has positive hysteresis.
(5) For V_{OH} and V_{OL} relation to output variants refer to **Timing Figures after the Timing Requirement Table**

7.6 Timing Requirements

At $V_{DD(MIN)} \le V_{DD} \le V_{DD\ (MAX)}$, CTR1/$\overline{\text{MR}}$ = CTR2/$\overline{\text{MR}}$ = CTS1 = CTS2 = open (1), output reset pull-up resistor R_{PU} = 10 kΩ, voltage V_{PU} = 5.5V, and C_{LOAD} = 10 pF. VDD and SENSE slew rate = 1V / µs. The operating free-air temperature range T_A = – 40°C to 125°C, unless otherwise noted. Typical values are at T_A = 25°C and VDD = 16 V and V_{IT} = 6.5 V (V_{IT} refers to either V_{ITN} or V_{ITP}).

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Common timing parameters						
t_{CTR}	Reset release time delay (CTR1/$\overline{\text{MR}}$, CTR2/$\overline{\text{MR}}$) (2)	VIT = 2.7 V to 36 V C_{CTR1} = C_{CTR2} = Open 20% Overdrive from Hysteresis			100	µs
		VIT = 800 mV C_{CTR1} = C_{CTR2} = Open 20% Overdrive from Hysteresis			40	µs
t_{CTS}	Sense detect time delay (CTS1, CTS2) (3)	VIT = 2.7 V to 36 V C_{CTS1} = C_{CTS2} = Open 20% Overdrive from V_{IT}		34	90	µs
		VIT = 800 mV C_{CTS1} = C_{CTS2} = Open 20% Overdrive from V_{IT}		8	17	µs
t_{SD}	Startup Delay (4)	$C_{CTR1/\overline{MR}}$ = $C_{CTR2/\overline{MR}}$ = Open			2	ms

(1) C_{CTR1} = Reset delay channel 1, C_{CTR2} = Reset delay channel 2,
C_{CTS1} = Sense delay channel 1, C_{CTS2} = Sense delay channel 2

(2) **CTR Reset detect time delay:**
Overvoltage active-LOW output is measure from $V_{ITP\ -\ HYS}$ to V_{OH}
Undervoltage active-LOW output is measure from $V_{ITN\ +\ HYS}$ to V_{OH}
Overvoltage active-HIGH output is measure from $V_{ITP\ -\ HYS}$ to V_{OL}
Undervoltage active-HIGH output is measure from $V_{ITN\ +\ HYS}$ to V_{OL}

(3) **CTS Sense detect time delay:**
Active-low output is measure from V_{IT} to V_{OL} (or V_{Pullup})
Active-high output is measured from V_{IT} to V_{OH}
V_{IT} refers to either V_{ITN} or V_{ITP}

(4) During the power-on sequence, VDD must be at or above $V_{DD\ (MIN)}$ for at least t_{SD} before the output is in the correct state based on V_{SENSE}.
t_{SD} time includes the propagation delay (C_{CTR1} = C_{CTR2} = Open). Capaicitor in C_{CTR1} or C_{CTR2} will add time to t_{SD}.

7.7 Timing Diagrams

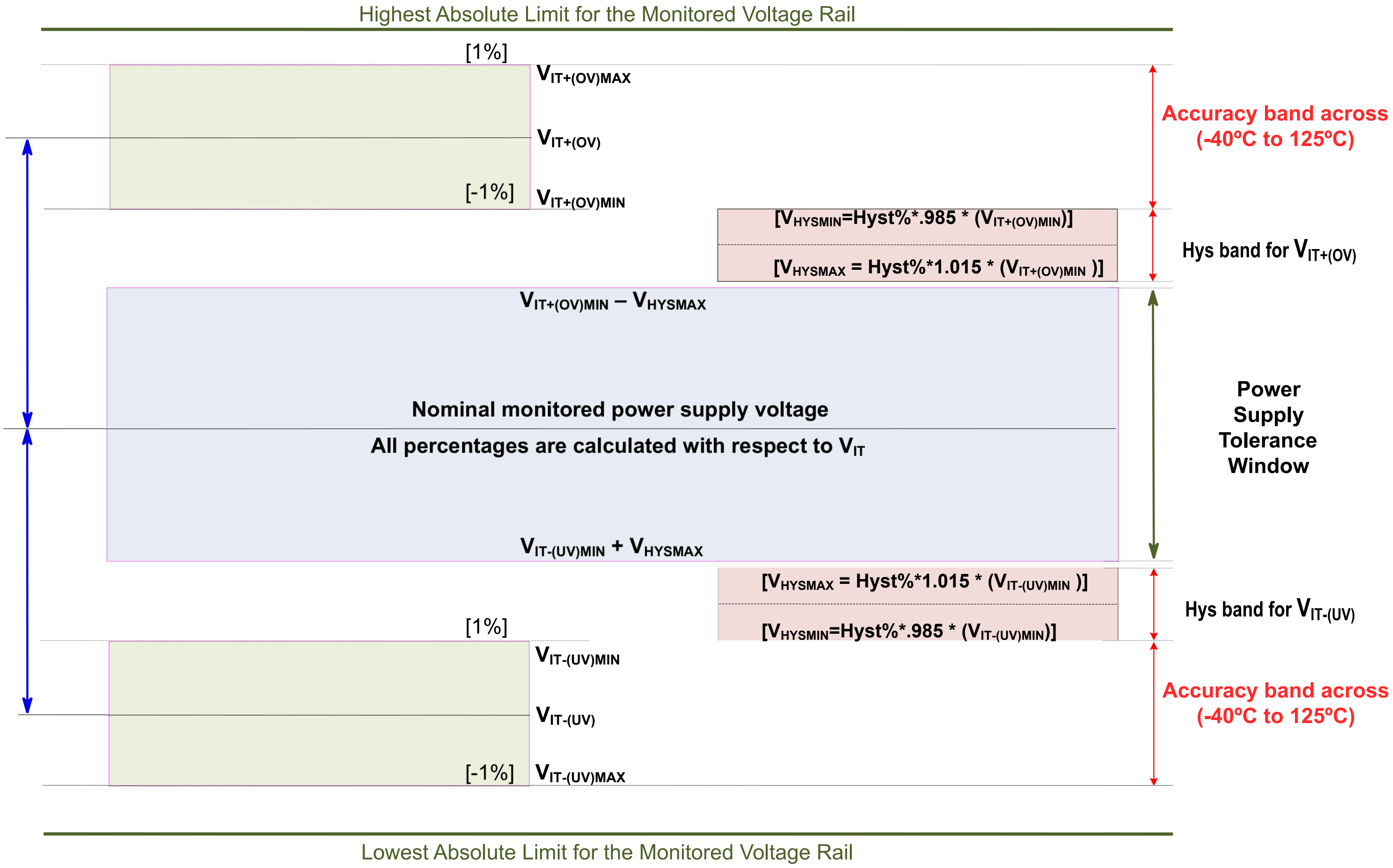
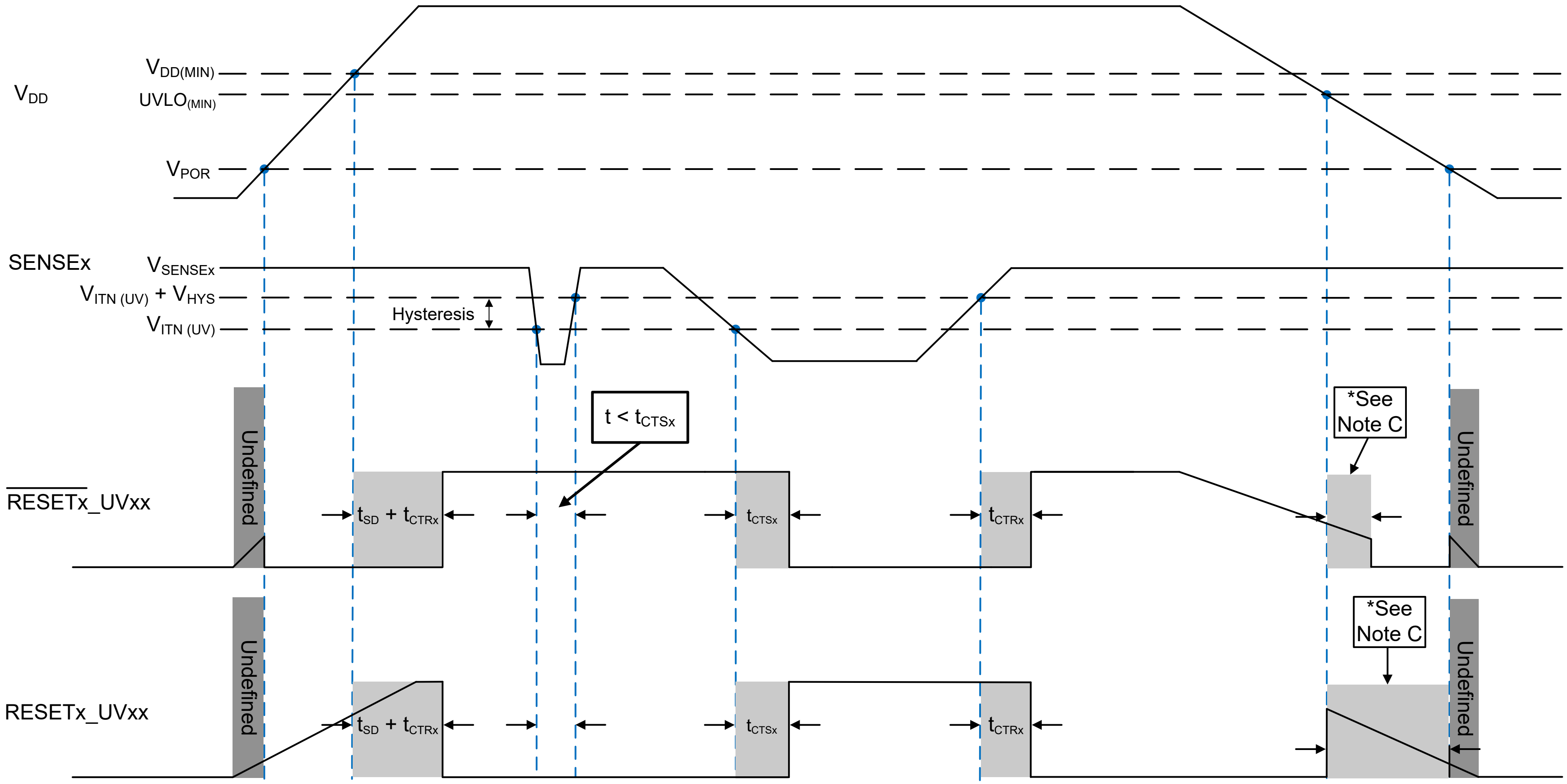


図 7-1. Voltage Threshold and Hysteresis Accuracy

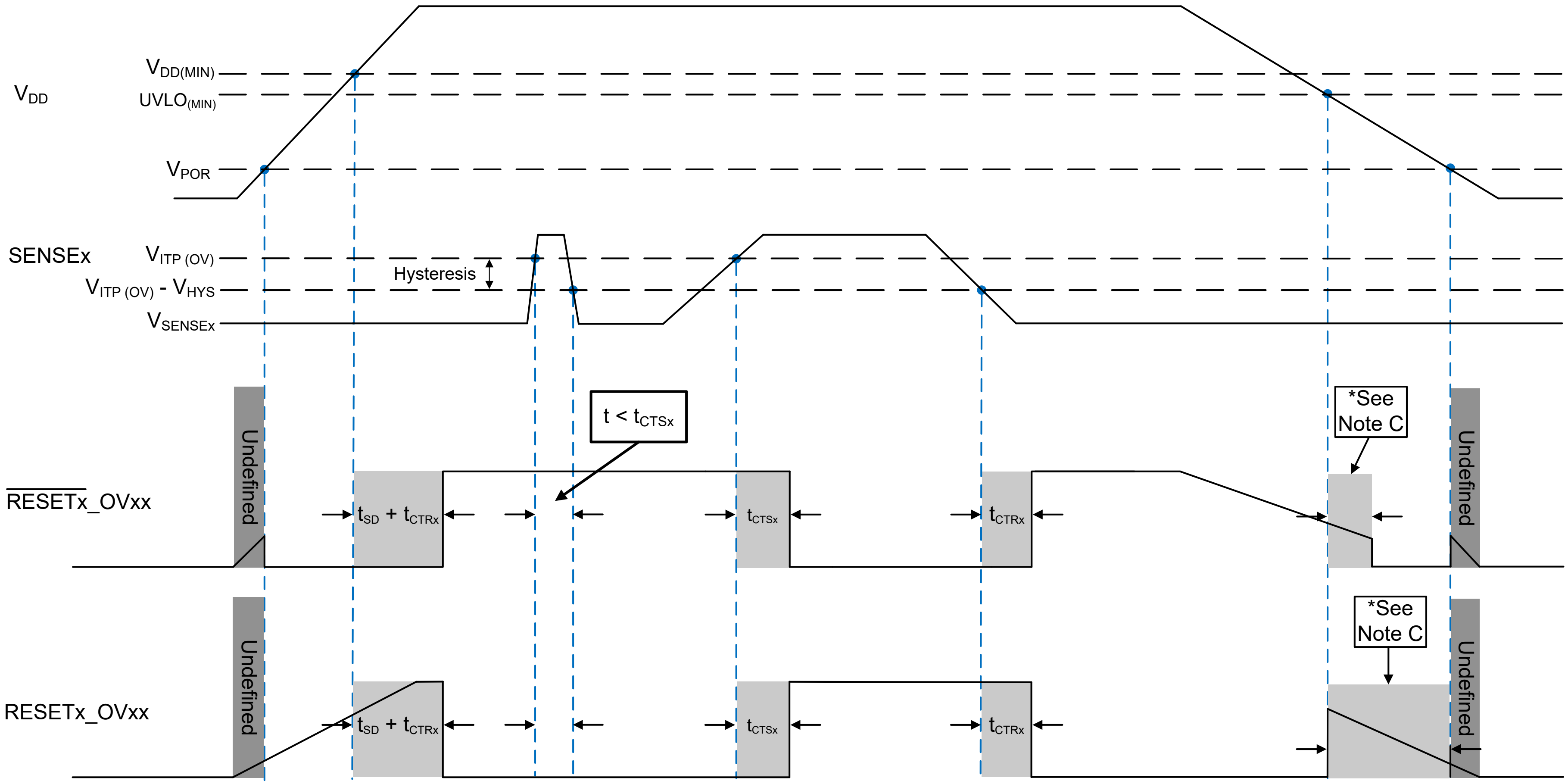


A. For open-drain output option, the timing diagram assumes the $\overline{\text{RESETx}}$_UVOD / RESETx_UVOD pin is connected via an external pull-up resistor to VDD.

B. Be advised that 図 7-2 shows the VDD falling slew rate is slow or the VDD decay time is much larger than the propagation detect delay (t_{CTRx}) time.

C. $\overline{\text{RESETx}}$_UVxx / RESETx_UVxx is asserted when VDD goes below the $UVLO_{(MIN)}$ threshold after the time delay, t_{CTRx}, is reached.

図 7-2. SENSEx Undervoltage (UV) Timing Diagram



A. For open-drain output option, the timing diagram assumes the $\overline{\text{RESETx}}$_OVOD / RESETx_OVOD pin is connected via an external pull-up resistor to VDD.

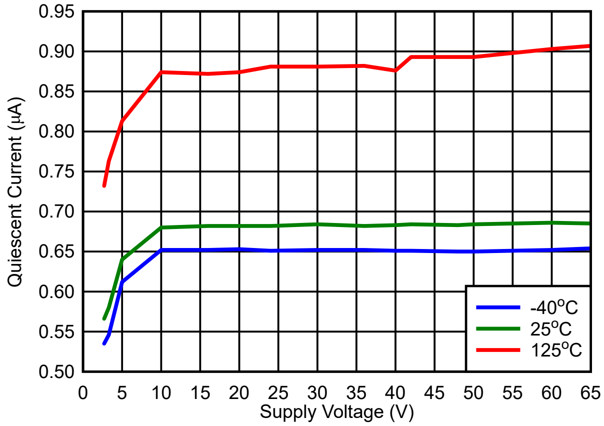
B. Be advised that 図 7-3 shows the VDD falling slew rate is slow or the VDD decay time is much larger than the propagation detect delay (t_{CTRx}) time.

C. $\overline{\text{RESETx}}$_OVxx / RESETx_OVxx is asserted when VDD goes below the $UVLO_{(MIN)}$ threshold after the time delay, t_{CTRx}, is reached.

図 7-3. SENSEx Overvoltage (OV) Timing Diagram

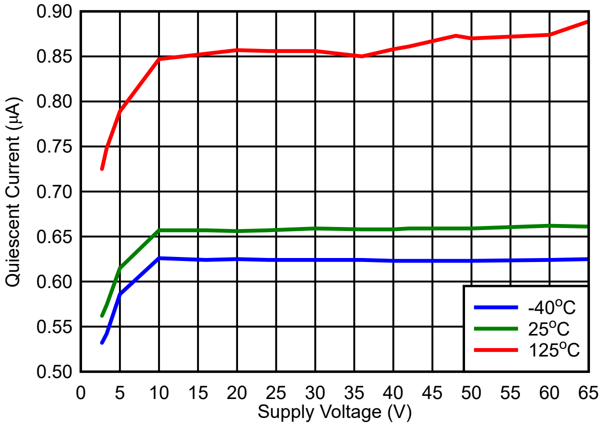
7.8 Typical Characteristics

Typical characteristics show the typical performance of the TPS38-Q1 device. Test conditions are T_A = 25°C, R_{PU} = 100 kΩ, C_{Load} = 50 pF, unless otherwise noted.



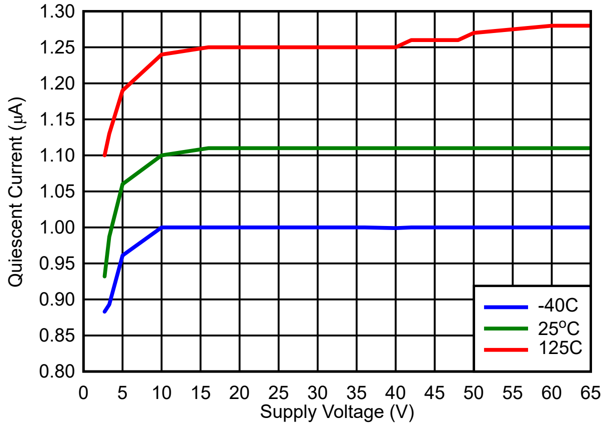
$\overline{\text{RESET}}$ = High, V_{IT} = 2.7 V

図 7-4. V_{DD} vs I_{DD} ($\overline{\text{RESET}}$ = High, V_{IT} = 2.7 V)



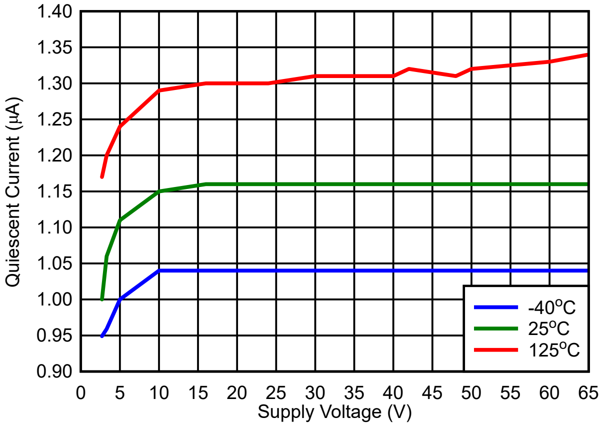
$\overline{\text{RESET}}$ = Low, V_{IT} = 2.7 V

図 7-5. V_{DD} vs I_{DD} ($\overline{\text{RESET}}$ = Low, V_{IT} = 2.7 V)



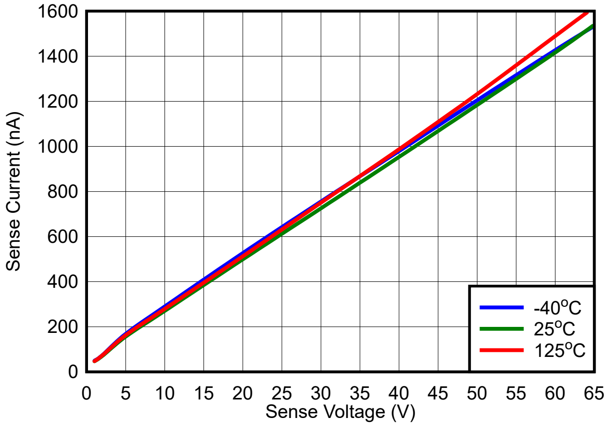
$\overline{\text{RESET}}$ = High, V_{IT} = 0.8 V

図 7-6. V_{DD} vs I_{DD} ($\overline{\text{RESET}}$ = High, V_{IT} = 0.8 V)



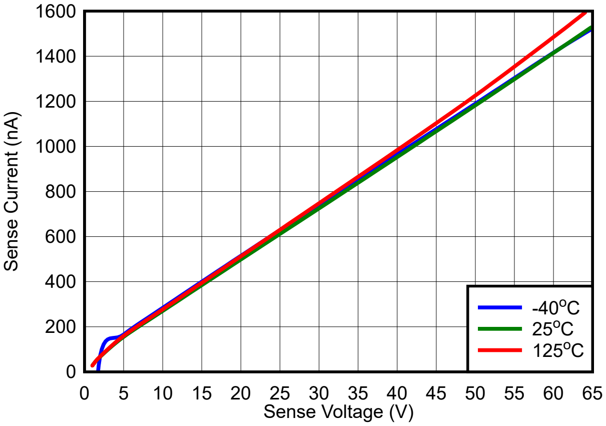
$\overline{\text{RESET}}$ = Low, V_{IT} = 0.8 V

図 7-7. V_{DD} vs I_{DD} ($\overline{\text{RESET}}$ = Low, V_{IT} = 0.8 V)



V_{DD} = 2.7 V

図 7-8. V_{SENSE} vs I_{SENSE}

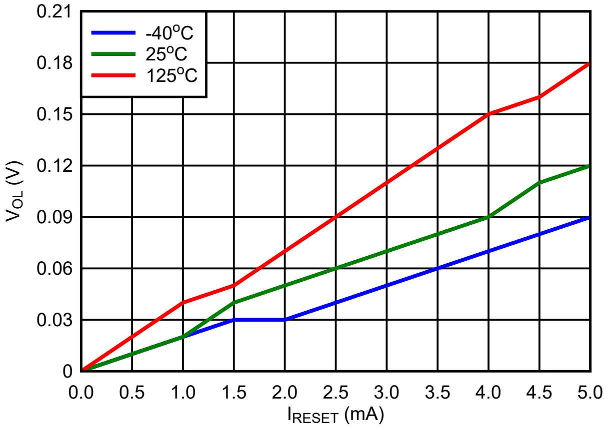


V_{DD} = 65 V

図 7-9. V_{SENSE} vs I_{SENSE}

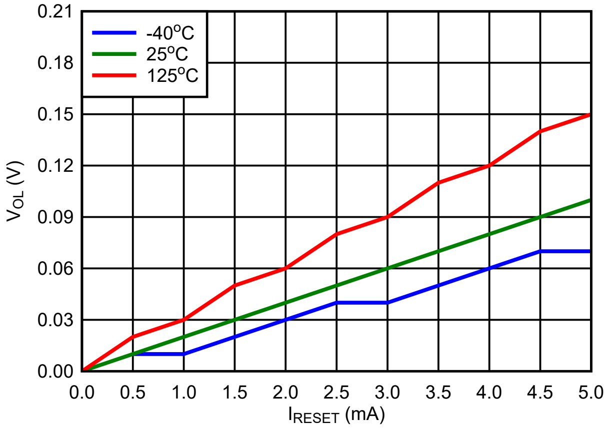
7.8 Typical Characteristics (continued)

Typical characteristics show the typical performance of the TPS38-Q1 device. Test conditions are T_A = 25°C, R_{PU} = 100 kΩ, C_{Load} = 50 pF, unless otherwise noted.



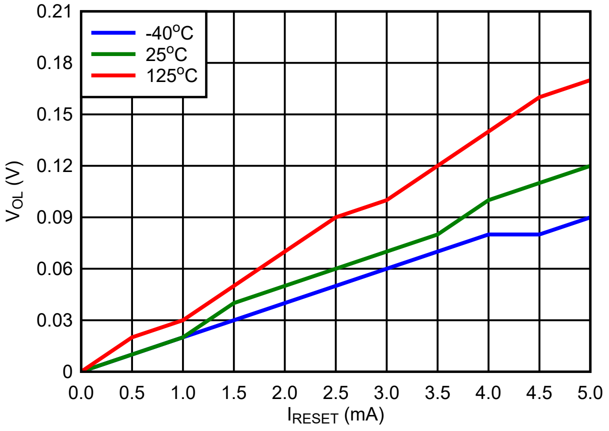
V_{DD} = 2.7 V

図 7-10. Open-Drain Active Low V_{OL} vs I_{RESET}



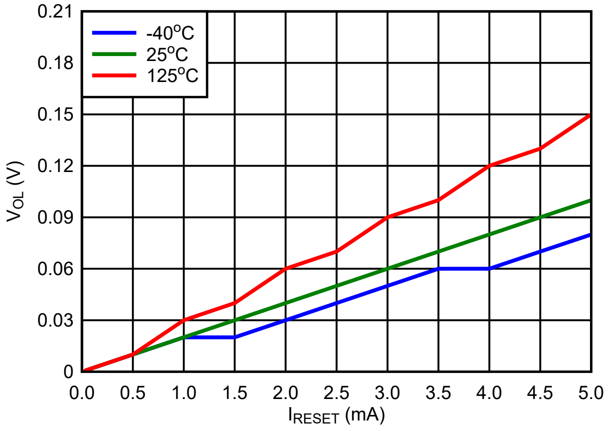
V_{DD} = 65 V

図 7-11. Open-Drain Active Low V_{OL} vs I_{RESET}



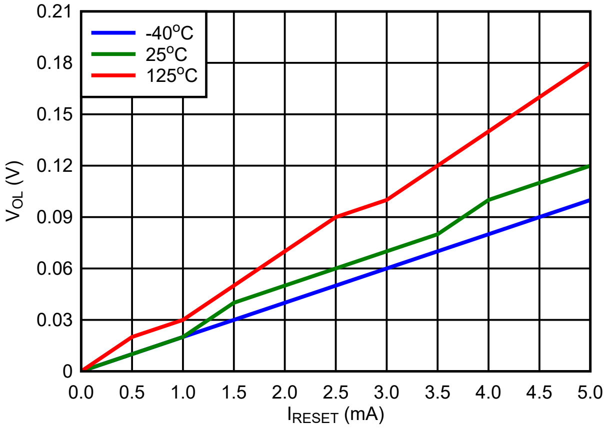
V_{DD} = 2.7 V

図 7-12. Open-Drain Active High V_{OL} vs I_{RESET}



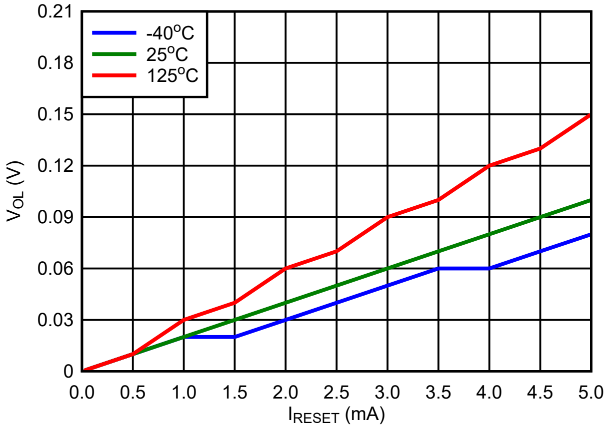
V_{DD} = 65 V

図 7-13. Open-Drain Active High V_{OL} vs I_{RESET}



V_{DD} = 2.7 V

図 7-14. Push-Pull Active High V_{OL} vs I_{RESET}



V_{DD} = 65 V

図 7-15. Push-Pull Active High V_{OL} vs I_{RESET}

7.8 Typical Characteristics (continued)

Typical characteristics show the typical performance of the TPS38-Q1 device. Test conditions are T_A = 25°C, R_{PU} = 100 kΩ, C_{Load} = 50 pF, unless otherwise noted.

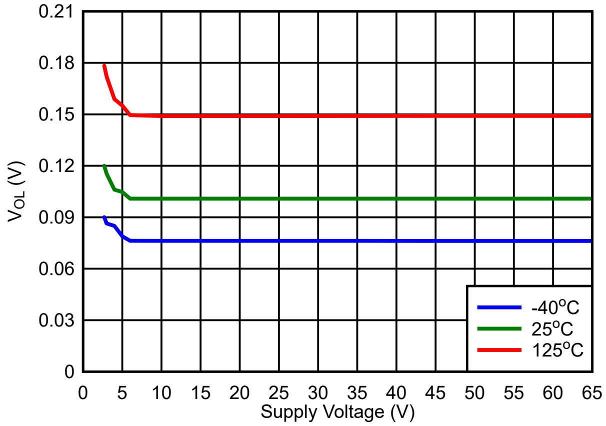


図 7-16. Open-Drain Active Low V_{OL} vs V_{DD}

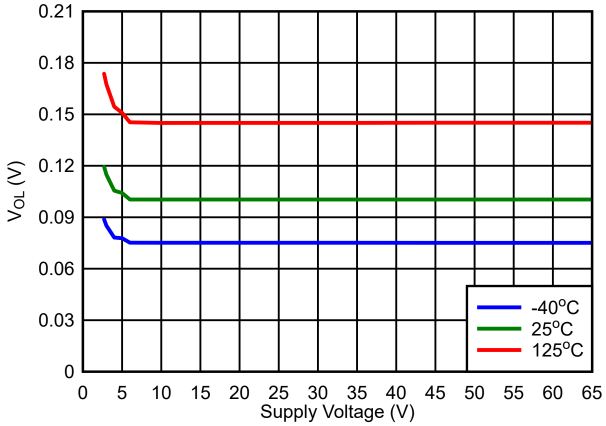


図 7-17. Open-Drain Active High V_{OL} vs V_{DD}

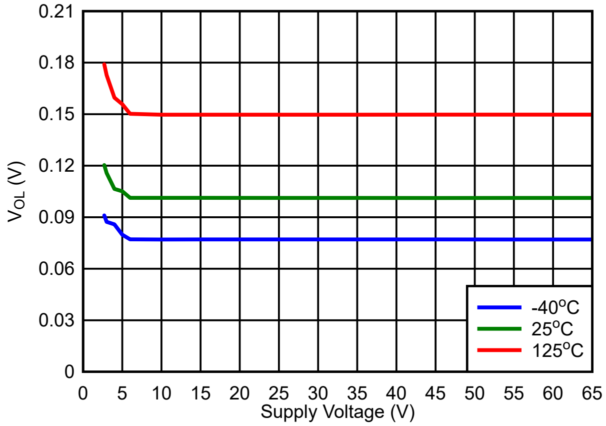


図 7-18. Push-Pull Active Low V_{OL} vs V_{DD}

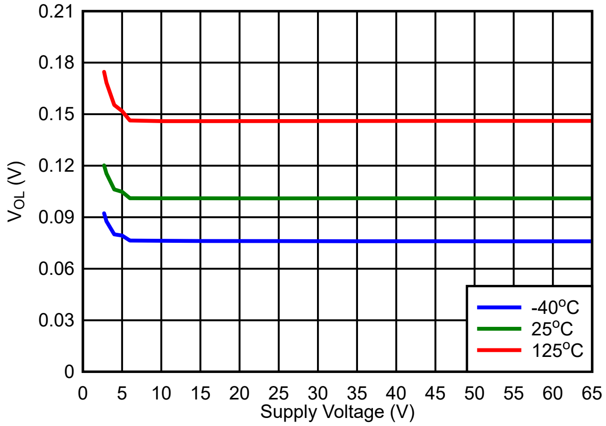


図 7-19. Push-Pull Active High V_{OL} vs V_{DD}

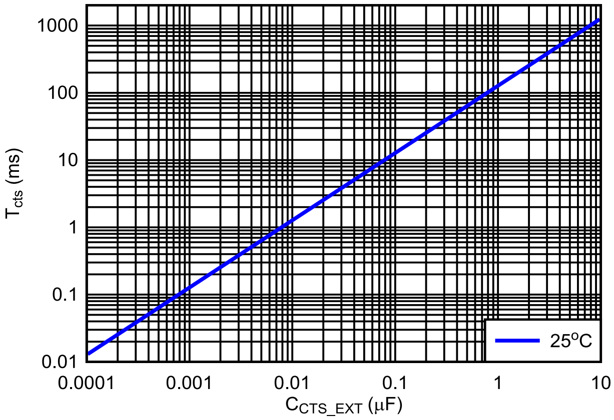


図 7-20. T_{CTS} vs C_{CTS}

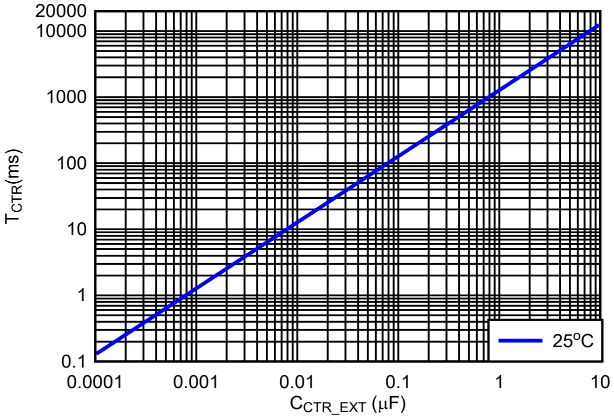


図 7-21. T_{CTR} vs C_{CTR}

8 Detailed Description

8.1 Overview

The TPS38-Q1 is a family of high voltage and low quiescent current reset IC with fixed threshold voltage. Voltage divider is integrated to eliminate the need for external resistors and eliminate leakage current that comes with resistor dividers. However, it can also support external resistor if required by application, the lowest threshold 800 mV (bypass internal resistor ladder) is recommenced for external resistors use case to take advantage of faster detection time and lower I_{SENSE} current.

VDD, SENSE and RESET pins can support 65 V continuous operation; both VDD and SENSE voltage levels can be independent of each other, meaning VDD pin can be connected at 2.7 V while SENSE pins are connected to a higher voltage. One thing of note, the TPS38-Q1 does not have clamps within the device so external circuits or devices must be added to limit the voltages to the absolute max limit.

Additional features include programmable sense time delay (CTS1, CTS2) and reset delay time and manual reset (CTR1 / $\overline{MR}$, CTR2 / $\overline{MR}$).

8.2 Functional Block Diagram

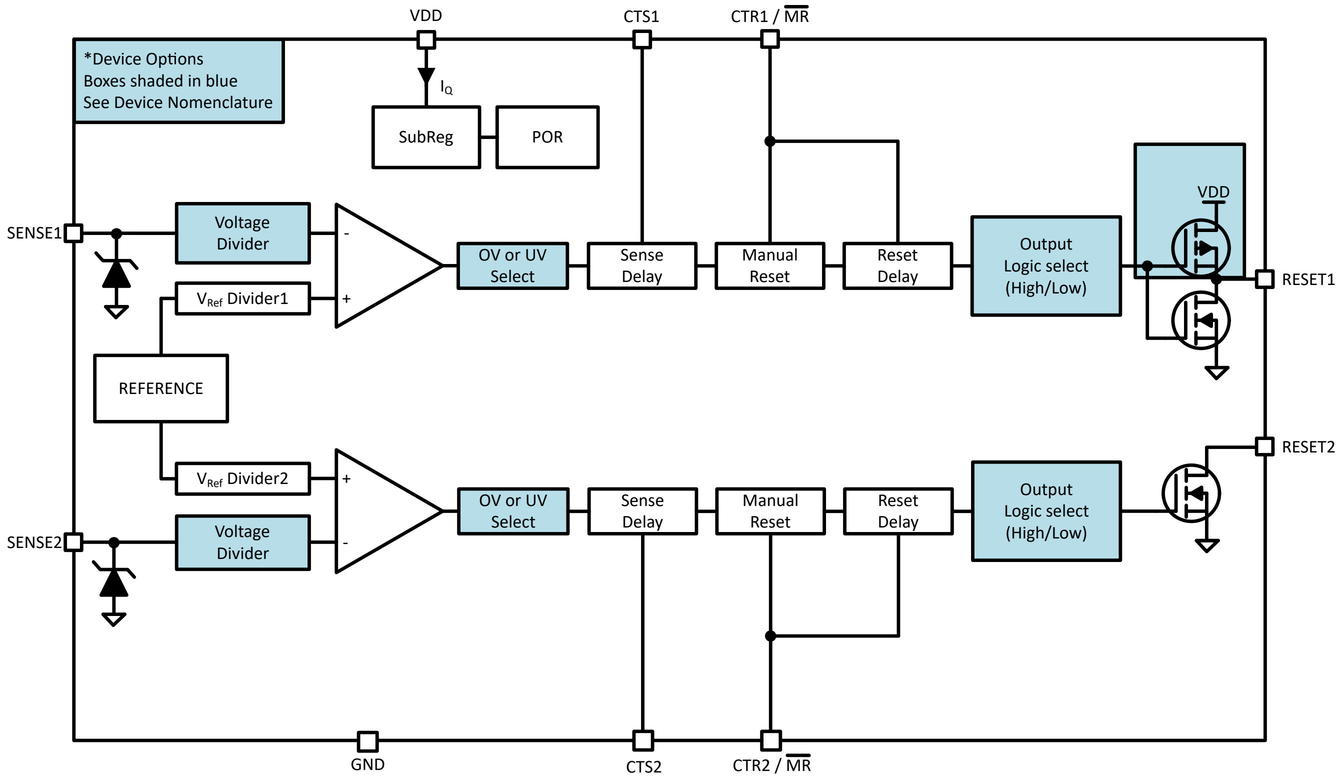


図 8-1. Functional Block Diagram

Refer to セクション 5 for complete list of topologies and output logic combinations.

8.3 Feature Description

8.3.1 Input Voltage (VDD)

VDD operating voltage ranges from 2.7 V to 65 V. An input supply capacitor is not required for this device; however, if the input supply is noisy good analog practice is to place a 0.1 µF capacitor between the VDD and GND.

VDD needs to be at or above $V_{DD(MIN)}$ for at least the start-up time delay (t_{SD}) for the device to be fully functional.

VDD voltage is independent of V_{SENSE} and V_{RESET}, meaning that VDD can be higher or lower than the other pins.

8.3.1.1 Undervoltage Lockout ($V_{POR} < V_{DD} <$ UVLO)

When the voltage on VDD is less than the UVLO voltage, but greater than the power-on reset voltage (V_{POR}), the output pins will be in reset, regardless of the voltage at SENSE pins.

8.3.1.2 Power-On Reset ($V_{DD} < V_{POR}$)

When the voltage on VDD is lower than the power on reset voltage (V_{POR}), the output signal is undefined and is not to be relied upon for proper device function.

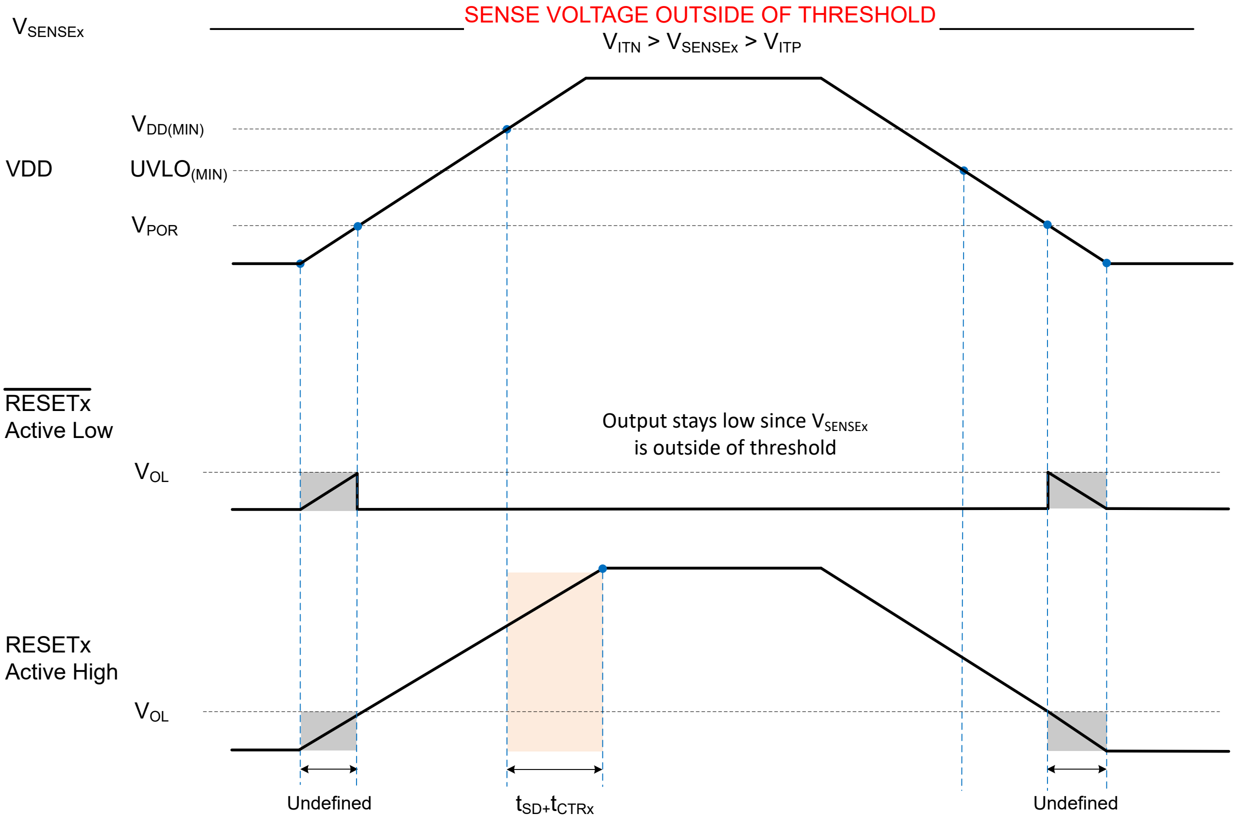


図 8-2. Power Cycle (SENSE Outside of Nominal Voltage)

図 8-2 assumes an external pull-up resistor is connected to the reset pin via VDD.

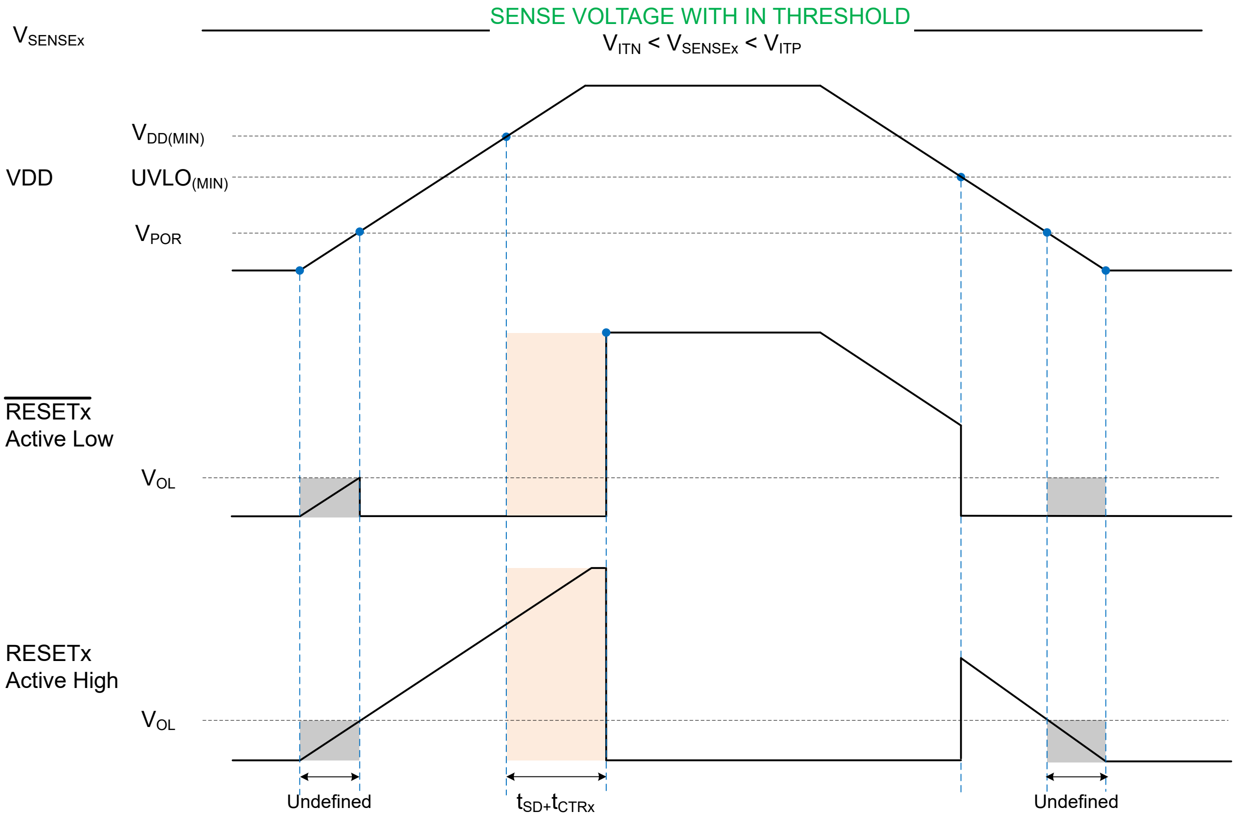


図 8-3. Power Cycle (SENSE Within Nominal Voltage)

図 8-3 assumes an external pull-up resistor is connected to the reset pin via VDD.

8.3.2 SENSE

The TPS38-Q1 high voltage family integrates two voltage comparators, a precision reference voltage and trimmed resistor divider. This configuration optimizes device accuracy because all resistor tolerances are accounted for in the accuracy and performance specifications. Device also has built-in hysteresis that provides noise immunity and ensures stable operation.

Channels are independent of each other, meaning that SENSE1 and SENSE2 and respective outputs can be connected to different voltage rails.

Although not required in most cases, for noisy applications good analog design practice is to place a 1 nF to 10 nF bypass capacitor at the SENSEx inputs in order to reduce sensitivity to transient voltages on the monitored signal. SENSE1 and SENSE2 pins can be connected directly to VDD pin.

8.3.2.1 SENSE Hysteresis

The TPS38-Q1 has built-in hysteresis to avoid erroneous output reset release. The hysteresis is opposite to the threshold voltage; for overvoltage options the hysteresis is subtracted from the positive threshold (V_{ITP}), for undervoltage options hysteresis is added to the negative threshold (V_{ITN}).

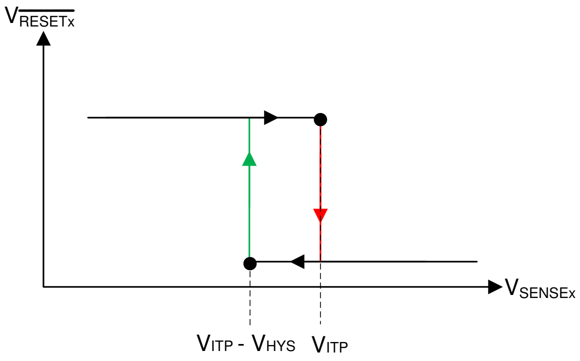


図 8-4. Hysteresis (Overvoltage Active-Low)

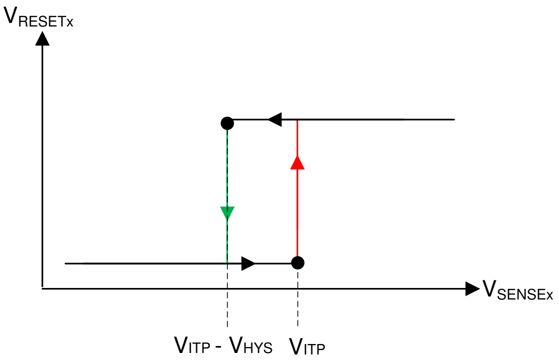


図 8-5. Hysteresis (Overvoltage Active-High)

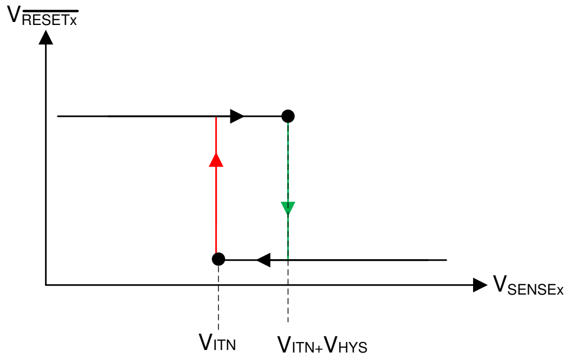


図 8-6. Hysteresis (Undervoltage Active-High)

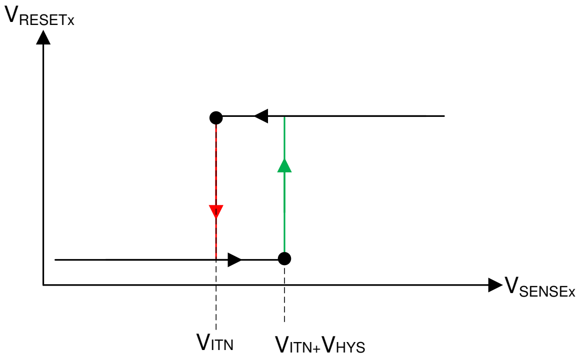


図 8-7. Hysteresis (Undervoltage Active-Low)

表 8-1. Common Hysteresis Lookup Table

TARGET			DEVICE ACTUAL HYSTERESIS OPTION
DETECT THRESHOLD	TOPOLOGY	RELEASE VOLTAGE (V)	
18.0 V	Overvoltage	17.5 V	-3%
18.0 V	Overvoltage	16.0 V	-11%
17.0 V	Overvoltage	16.5 V	-3%
16.0 V	Overvoltage	15.0 V	-6%
15.0 V	Overvoltage	14.0 V	-7%
6.0 V	Undervoltage	6.5 V	0.5 V
5.5 V	Undervoltage	6 V	0.5 V
8 V	Undervoltage	9 V	1 V
5 V	Undervoltage	7.5 V	2.5 V

表 8-1 shows a sample of hysteresis and voltage options for the TPS38-Q1. For threshold voltages ranging from 2.7 V to 8 V, one option is to select a fixed hysteresis value ranging from 0.5 V to 2.5 V in increments of 0.5 V. Additionally, a second option can be selected where the hysteresis value is a percentage of the threshold voltage. The percentage of voltage hysteresis ranges from 2% to 13%.

Knowing the amount of hysteresis voltage, the release voltage for the undervoltage (UV) channel is ($V_{ITN(UV)}$ + V_{HYS}) and for the overvoltage (OV) channel is ($V_{ITP(OV)}$ - V_{HYS}). For a visual understanding of the UV and OV release voltage, see 図 7-2 and 図 7-3 . The accuracy of the release voltage, or stated in the セクション 7.5 as *Hysteresis Accuracy* is ±1.5%. Expanding what is shown in 表 8-1, below are a few voltage hysteresis examples that include the hysteresis accuracy:

Undervoltage (UV) Channel

V_{ITN} = 0.8 V

Voltage Hysteresis (V_{HYS}) = 5% = 40 mV

Hysteresis Accuracy = ±1.5% = 39.4 mV or 40.6 mV

Release Voltage = V_{ITN} + V_{HYS} = 839.4 mV to 840.6 mV

Overvoltage (OV) Channel

V_{ITP} = 8 V

Voltage Hysteresis (V_{HYS}) = 2 V

Hysteresis Accuracy = ±1.5% = 1.97 V or 2.03 V

Release Voltage = V_{ITP} − V_{HYS} = 5.97 V to 6.03V

8.3.3 Output Logic Configurations

TPS38-Q1 has two channels with separate sense pins and reset pins that can be configured independently of each other. Channel 1 is available as Open-Drain and Push-Pull while channel 2 is only available as Open-Drain topology.

The available output logic configuration combinations are shown in Table 表 8-2.

表 8-2. TPS38-Q1 Output Logic

DESCRIPTION	NOMENCLATURE	VALUE	
GPN	**TPS38-Q1 (+ topology)**	**CHANNEL 1**	**CHANNEL 2**
Topology (OV and UV only) both channels are either OV or UV • UV = Undervoltage • OV = Overvoltage • PP = Push-Pull • OD = Open-Drain • L = Active low • H = Active high	TPS38A-Q1	UV OD L	UV OD L
	TPS38B-Q1	UV PP L	UV OD L
	TPS38D-Q1	UV PP L	UV OD H
	TPS38E-Q1	UV PP H	UV OD H
	TPS38F-Q1	UV PP H	UV OD L
	TPS38G-Q1	UV OD H	UV OD H
	TPS38H-Q1	UV OD H	UV OD L
	TPS38J-Q1	OV OD L	OV OD L
	TPS38M-Q1	OV PP L	OV OD L
	TPS38N-Q1	OV PP L	OV OD H
	TPS38O-Q1	OV PP H	OV OD H
	TPS38P-Q1	OV PP H	OV OD L

8.3.3.1 Open-Drain

Open-drain output requires an external pull-up resistor to hold the voltage high to the required voltage logic. Connect the pull-up resistor to the proper voltage rail to enable the output to be connected to other devices at the correct interface voltage levels.

To select the right pull-up resistor consider system V_{OH} and the (I_{lkg}) current provided in the electrical characteristics, high resistors values will have a higher voltage drop affecting the output voltage high. The open-drain output can be connected as a wired-AND logic with other open-drain signals such as another TPS38-Q1 open-drain output pin.

8.3.3.2 Push-Pull

Push-Pull output does not require an external resistor since is the output is internally pulled-up to VDD during V_{OH} condition and output will be connected to GND during V_{OH} condition.

8.3.3.3 Active-High (RESET)

RESET (active-high), denoted with no bar above the pin label. RESET remains low (V_{OL}, deasserted) as long as sense voltage is in normal operation within the threshold boundaries and VDD voltage is above UVLO. To assert a reset sense pins needs to meet the condition below:

- For undervoltage variant the SENSE voltage need to cross the lower boundary (V_{ITN}).
- For overvoltage variant the SENSE voltage needs to cross the upper boundary (V_{ITP}).

8.3.3.4 Active-Low ($\overline{\text{RESET}}$)

$\overline{\text{RESET}}$ (active low) denoted with a bar above the pin label. $\overline{\text{RESET}}$ remains high voltage (V_{OH}, deasserted) (open drain variant V_{OH} is measured against the pullup voltage) as long as sense voltage is in normal operation within the threshold boundaries and VDD voltage is above UVLO. To assert a reset sense pins needs to meet the condition below:

- For undervoltage variant the SENSE voltage need to cross the lower boundary (V_{ITN}).
- For overvoltage variant the SENSE voltage needs to cross the upper boundary (V_{ITP}).

8.3.4 User-Programmable Reset Time Delay

The TPS38-Q1 has an adjustable reset release time delay with external capacitors. Channel timing is independent of each other.

- A capacitor in CTR1 / $\overline{\text{MR}}$ program the reset time delay of Output 1.
- A capacitor in CTR2 / $\overline{\text{MR}}$ program the reset time delay of Output 2.
- No capacitor on these pins gives the fastest reset delay time indicated in the セクション 7.6.

8.3.4.1 Reset Time Delay Configuration

The time delay (t_{CTR}) can be programmed by connecting a capacitor between CTR1 pin and GND, CTR2 for channel 2. In this section CTRx represent either channel 1 or channel 2.

The relationship between external capacitor $C_{CTRx\_EXT\ (typ)}$ and the time delay $t_{CTRx\ (typ)}$ is given by 式 1.

$$t_{CTRx\ (typ)} = -\ln\ (0.28) \times R_{CTRx\ (typ)} \times C_{CTRx\_EXT\ (typ)} + t_{CTRx\ (no\ cap)} \tag{1}$$

$R_{CTRx\ (typ)}$ = is in kilo ohms (kOhms)

$C_{CTRx\_EXT\ (typ)}$ = is given in microfarads (µF)

$t_{CTRx\ (typ)}$ = is the reset time delay in (ms)

The reset delay varies according to three variables: the external capacitor (C_{CTRx_EXT}), CTR pin internal resistance (R_{CTRx}) provided in セクション 7.5, and a constant. The minimum and maximum variance due to the constant is show in 式 2 and 式 3:

$$t_{CTRx\ (min)} = -\ln\ (0.31) \times R_{CTRx\ (min)} \times C_{CTRx\_EXT\ (min)} + t_{CTRx\ (no\ cap\ (min))} \tag{2}$$

$$t_{CTRx\ (max)} = -\ln\ (0.25) \times R_{CTRx\ (max)} \times C_{CTRx\_EXT\ (max)} + t_{CTRx\ (no\ cap\ (max))} \tag{3}$$

The recommended maximum reset delay capacitor for the TPS38-Q1 is limited to 10 µF as this ensures enough time for the capacitor to fully discharge when a voltage fault occurs. Also, having a too large of a capacitor value can cause very slow charge up (rise times) and system noise can cause the the internal circuit to trip earlier or later near the threshold. This leads to variation in time delay where it can make the delay accuracy worse in the presence of system noise.

When a voltage fault occurs, the previously charged up capacitor discharges and if the monitored voltage returns from the fault condition before the delay capacitor discharges completely, the delay will be shorter than expected. The capacitor will begin charging from a voltage above zero and resulting in shorter than expected time delay. A larger delay capacitor can be used so long as the capacitor has enough time to fully discharge during the duration of the voltage fault. To ensure the capacitor is fully discharged, the time period or duration of the voltage fault needs to be greater than 5% of the programmed reset time delay.

8.3.5 User-Programmable Sense Delay

TPS38-Q1 has adjustable sense release time delay with external capacitors. Channel timing are independent of each other. Sense delay is used as a de-glitcher or ignoring known transients.

- A capacitor in CTS1 program the excursion detection on SENSE1.
- A capacitor in CTS2 program the excursion detection on SENSE2.
- No capacitor on these pins gives the fastest detection time indicated in the セクション 7.6.

8.3.5.1 Sense Time Delay Configuration

The time delay (t_{CTS}) can be programmed by connecting a capacitor between CTS1 pin and GND, CTS2 for channel 2. In this section CTSx represent either channel 1 or channel 2.

The relationship between external capacitor $C_{CTSx\_EXT\ (typ)}$ and the time delay $t_{CTSx\ (typ)}$ is given by 式 4.

$$t_{CTSx\ (typ)} = -\ln\ (0.28) \times R_{CTSx\ (typ)} \times C_{CTSx\_EXT\ (typ)} + t_{CTSx\ (no\ cap)} \tag{4}$$

R_{CTSx} = is in kilo ohms (kOhms)

C_{CTSX_EXT} = is given in microfarads (μF)

t_{CTSx} = is the sense time delay (ms)

The sense delay varies according to three variables: the external capacitor (C_{CTSx_EXT}), CTS pin internal resistance (R_{CTSx}) provided in セクション 7.5, and a constant. The minimum and maximum variance due to the constant is show in 式 5 and 式 6:

$$t_{CTSx\ (min)} = -\ln\ (0.31) \times R_{CTSx\ (min)} \times C_{CTSx\_EXT\ (min)} + t_{CTSx\ (no\ cap\ (min))} \tag{5}$$

$$t_{CTSx\ (max)} = -\ln\ (0.25) \times R_{CTSx\ (max)} \times C_{CTSx\_EXT\ (max)} + t_{CTSx\ (no\ cap\ (max))} \tag{6}$$

The recommended maximum sense delay capacitor for the TPS38-Q1 is limited to 10 μF as this ensures enough time for the capacitor to fully discharge when a voltage fault occurs. Also, having a too large of a capacitor value can cause very slow charge up (rise times) and system noise can cause the the internal circuit to trip earlier or later near the threshold. This leads to variation in time delay where it can make the delay accuracy worse in the presence of system noise.

When a voltage fault occurs, the previously charged up capacitor discharges and if the monitored voltage returns from the fault condition before the delay capacitor discharges completely, the delay will be shorter than expected. The capacitor will begin charging from a voltage above zero and resulting in shorter than expected time delay. A larger delay capacitor can be used so long as the capacitor has enough time between fault events to fully discharge during the duration of the voltage fault. To ensure the capacitor is fully discharged, the time period or time duration between fault events needs to be greater than 10% of the programmed sense time delay.

8.3.6 Manual RESET (CTR1 / $\overline{\text{MR}}$) and (CTR2 / $\overline{\text{MR}}$) Input

The manual reset input allows a processor or other logic circuits to initiate a reset. In this section $\overline{\text{MR}}$ is a generic reference to (CTR1 / $\overline{\text{MR}}$) and (CTR2 / $\overline{\text{MR}}$). A logic low on $\overline{\text{MR}}$ causes $\overline{\text{RESET1}}$ to assert on reset output. After $\overline{\text{MR}}$ is left floating, $\overline{\text{RESET1}}$ will release the reset if the voltage at SENSE1 pin is at nominal voltage. $\overline{\text{MR}}$ should not be driven high, this pin should be left floating or connected to a capacitor to GND, this pin can be left unconnected if is not used.

If the logic driving the $\overline{\text{MR}}$ cannot tri-state (floating and GND) then a logic-level FET should be used as illustrated in 図 8-8.

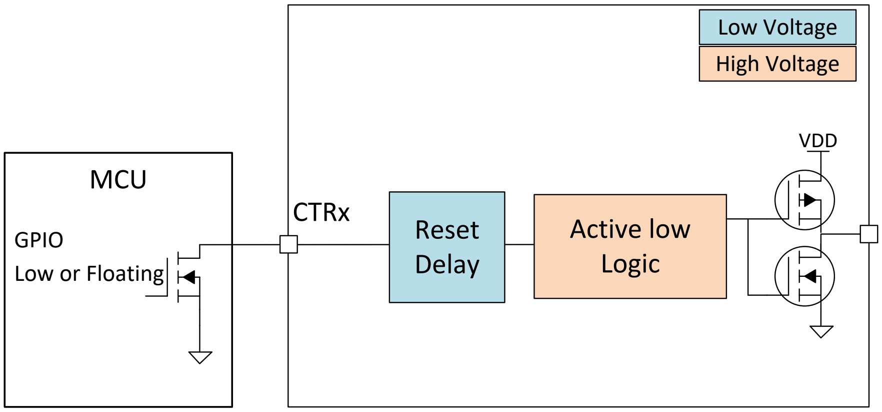


図 8-8. Manual Reset Implementation

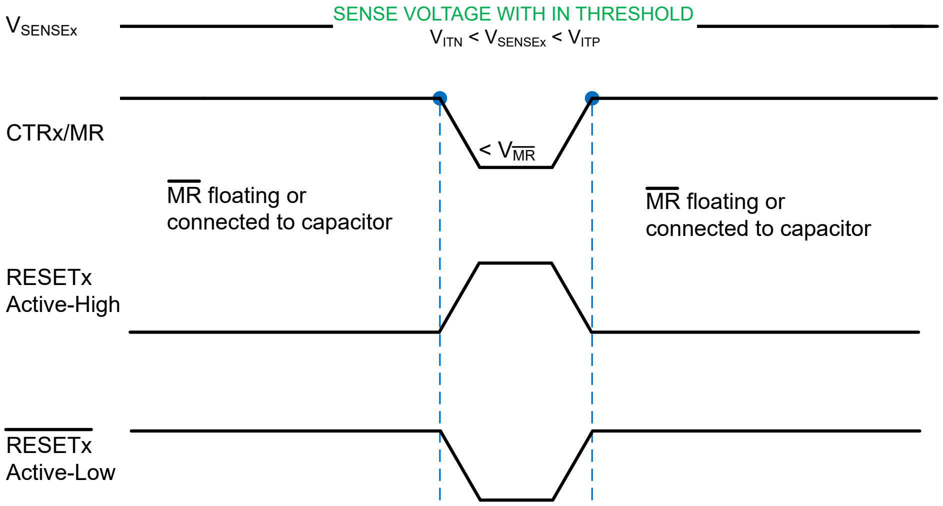


図 8-9. Manual Rest Timing Diagram

表 8-3. $\overline{\text{MR}}$ Functional Table

$\overline{\text{MR}}$	SENSE ON NOMINAL VOLTAGE	RESET STATUS
Low	Yes	Reset asserted
Floating	Yes	Fast reset release when SENSE voltage goes back to nominal voltage
Capacitor	Yes	Programmable reset time delay
High	Yes	NOT Recommended

8.3.7 Adjustable Voltage Thresholds

式 7 illustrates an example of how to adjust the voltage threshold with external resistor dividers. The resistors can be calculated depending on the desired voltage threshold and device part number. TI recommends using the 0.8 V voltage threshold device when using an adjustable voltage variant. This variant bypasses the internal resistor ladder.

For example, consider a 12 V rail being monitored V_{MON} for undervoltage (UV) using channel 1 of the TPS38A010122DSKRQ1 variant. Using 式 7 and shown in 図 8-10, R_1 is the top resistor of the resistor divider that is between V_{MON} and V_{SENSE2}, R_2 is the bottom resistor that is between V_{SENSE2} and GND, V_{MON} is the voltage rail that is being monitored and V_{SENSE2} is the input threshold voltage. The monitored UV threshold, denoted as V_{MON-}, where the device will assert a reset signal occurs when $V_{SENSE2} = V_{IT-(UV)}$ or, for this example, V_{MON-} = 10.8V which is 90% from 12 V. Using 式 7 and assuming R_2 = 10kΩ, R_1 can be calculated shown in 式 8 where I_{R1} is represented in 式 9:

$$V_{SENSE2} = V_{MON-} \times (R_2 \div (R_1 + R_2)) \tag{7}$$

$$R_1 = (V_{MON-} - V_{SENSE2}) \div I_{R1} \tag{8}$$

$$I_{R1} = I_{R2} = V_{SENSE2} \div R_2 \tag{9}$$

Substituting 式 9 into 式 8 and solving for R_1 in 式 7, R_1 = 125kΩ. The TPS38A010122DSKRQ1 is typically meant to monitor a 0.8 V rail with ±2% voltage threshold hysteresis. For the reset signal to become deasserted, V_{MON} would need to go above $V_{IT-} + V_{HYS}$. For this example,
V_{MON} = 11.016 V when the reset signal becomes deasserted.

There are inaccuracies that must be taken into consideration while adjusting voltage thresholds. Aside from the tolerance of the resistor divider, there is an internal resistance of the SENSE pin that may affect the accuracy of the resistor divider. Although expected to be very high impedance, users are recommended to calculate the values for the design specifications. The internal SENSE resistance R_{SENSE} can be calculated by the SENSE voltage V_{SENSE} divided by the SENSE current I_{SENSE} as shown in 式 11. V_{SENSE} can be calculated using 式 7 depending on the resistor divider and monitored voltage. I_{SENSE} can be calculated using 式 10.

$$I_{SENSE} = [(V_{MON} - V_{SENSE}) \div R_1] - (V_{SENSE} \div R_2) \tag{10}$$

$$R_{SENSE} = V_{SENSE} \div I_{SENSE} \tag{11}$$

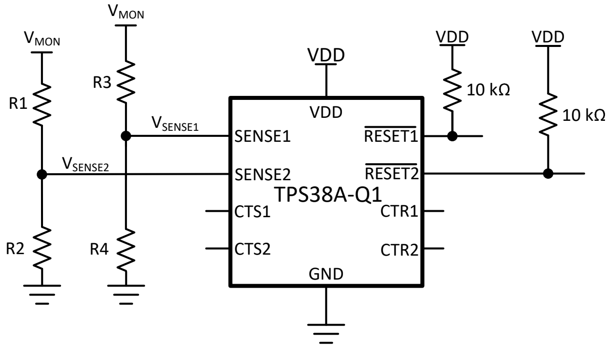


図 8-10. Adjustable Voltage Threshold with External Resistor Dividers

8.4 Device Functional Modes

表 8-4. Undervoltage Detect Functional Mode Truth Table

DESCRIPTION	SENSE		CTR (1) / $\overline{\text{MR}}$ PIN	VDD PIN	OUTPUT (2) ($\overline{\text{RESET}}$ PIN)
	PREVIOUS CONDITION	CURRENT CONDITION			
Normal Operation	SENSE > $V_{ITN(UV)}$	SENSE > $V_{ITN(UV)}$	Open or capacitor connected	$V_{DD} > V_{DD(MIN)}$	High
Undervoltage Detection	SENSE > $V_{ITN(UV)}$	SENSE < $V_{ITN(UV)}$	Open or capacitor connected	$V_{DD} > V_{DD(MIN)}$	Low
Undervoltage Detection	SENSE < $V_{ITN(UV)}$	SENSE > $V_{ITN(UV)}$	Open or capacitor connected	$V_{DD} > V_{DD(MIN)}$	Low
Normal Operation	SENSE < $V_{ITN(UV)}$	SENSE > $V_{ITN(UV)}$ + HYS	Open or capacitor connected	$V_{DD} > V_{DD(MIN)}$	High
Manual Reset	SENSE > $V_{ITN(UV)}$	SENSE > $V_{ITN(UV)}$	Low	$V_{DD} > V_{DD(MIN)}$	Low
UVLO Engaged	SENSE > $V_{ITN(UV)}$	SENSE > $V_{ITN(UV)}$	Open or capacitor connected	$V_{POR} < V_{DD} < V_{DD(MIN)}$	Low
Below V_{POR}, Undefined Output	SENSE > $V_{ITN(UV)}$	SENSE > $V_{ITN(UV)}$	Open or capacitor connected	$V_{DD} < V_{POR}$	Undefined

(1) Reset time delay is ignored in the truth table
(2) Open-drain active low output. External pull-up resistor to high voltage

表 8-5. Overvoltage Detect Functional Mode Truth Table

DESCRIPTION	SENSE		CTR (1) / $\overline{\text{MR}}$ PIN	VDD PIN	OUTPUT (2) ($\overline{\text{RESET}}$ PIN)
	PREVIOUS CONDITION	CURRENT CONDITION			
Normal Operation	SENSE < $V_{ITN(OV)}$	SENSE < $V_{ITN(OV)}$	Open or capacitor connected	$V_{DD} > V_{DD(MIN)}$	High
Overvoltage Detection	SENSE < $V_{ITN(OV)}$	SENSE > $V_{ITN(OV)}$	Open or capacitor connected	$V_{DD} > V_{DD(MIN)}$	Low
Overvoltage Detection	SENSE > $V_{ITN(OV)}$	SENSE < $V_{ITN(OV)}$	Open or capacitor connected	$V_{DD} > V_{DD(MIN)}$	Low
Normal Operation	SENSE > $V_{ITN(OV)}$	SENSE < $V_{ITN(OV)}$ - HYS	Open or capacitor connected	$V_{DD} > V_{DD(MIN)}$	High
Manual Reset	SENSE < $V_{ITN(OV)}$	SENSE < $V_{ITN(OV)}$	Low	$V_{DD} > V_{DD(MIN)}$	Low
UVLO Engaged	SENSE < $V_{ITN(OV)}$	SENSE < $V_{ITN(OV)}$	Open or capacitor connected	$V_{POR} < V_{DD} <$ UVLO	Low
Below V_{POR}, Undefined Output	SENSE < $V_{ITN(OV)}$	SENSE < $V_{ITN(OV)}$	Open or capacitor connected	$V_{DD} < V_{POR}$	Undefined

(1) Reset time delay is ignored in the truth table
(2) Open-drain active low output. External pull-up resistor to high voltage

9 Application and Implementation

注

以下のアプリケーション情報は、TI の製品仕様に含まれるものではなく、TI ではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

9.1 Adjustable Voltage Thresholds

式 12 illustrates an example of how to adjust the voltage threshold with external resistor dividers. The resistors can be calculated depending on the desired voltage threshold and device part number. TI recommends using the 0.8 V voltage threshold device when using an adjustable voltage variant. This variant bypasses the internal resistor ladder.

For example, consider a 12 V rail being monitored V_{MON} for undervoltage (UV) using channel 1 of the TPS38A010122DSKRQ1 variant. Using 式 12 and shown in 図 9-1, R_1 is the top resistor of the resistor divider that is between V_{MON} and V_{SENSE2}, R_2 is the bottom resistor that is between V_{SENSE2} and GND, V_{MON} is the voltage rail that is being monitored and V_{SENSE2} is the input threshold voltage. The monitored UV threshold, denoted as V_{MON-}, where the device will assert a reset signal occurs when $V_{SENSE2} = V_{IT-(UV)}$ or, for this example, $V_{MON-} = 10.8V$ which is 90% from 12 V. Using 式 12 and assuming $R_2 = 10k\Omega$, R_1 can be calculated shown in 式 13 where I_{R1} is represented in 式 14:

$$V_{SENSE2} = V_{MON-} \times (R_2 \div (R_1 + R_2)) \tag{12}$$

$$R_1 = (V_{MON-} - V_{SENSE2}) \div I_{R1} \tag{13}$$

$$I_{R1} = I_{R2} = V_{SENSE2} \div R_2 \tag{14}$$

Substituting 式 14 into 式 13 and solving for R_1 in 式 12, $R_1 = 125k\Omega$. The TPS38A010122DSKRQ1 is typically meant to monitor a 0.8 V rail with ±2% voltage threshold hysteresis. For the reset signal to become deasserted, V_{MON} would need to go above $V_{IT-} + V_{HYS}$. For this example,
$V_{MON} = 11.016$ V when the reset signal becomes deasserted.

There are inaccuracies that must be taken into consideration while adjusting voltage thresholds. Aside from the tolerance of the resistor divider, there is an internal resistance of the SENSE pin that may affect the accuracy of the resistor divider. Although expected to be very high impedance, users are recommended to calculate the values for the design specifications. The internal SENSE resistance R_{SENSE} can be calculated by the SENSE voltage V_{SENSE} divided by the SENSE current I_{SENSE} as shown in 式 16. V_{SENSE} can be calculated using 式 12 depending on the resistor divider and monitored voltage. I_{SENSE} can be calculated using 式 15.

$$I_{SENSE} = [(V_{MON} - V_{SENSE}) \div R_1] - (V_{SENSE} \div R_2) \tag{15}$$

$$R_{SENSE} = V_{SENSE} \div I_{SENSE} \tag{16}$$

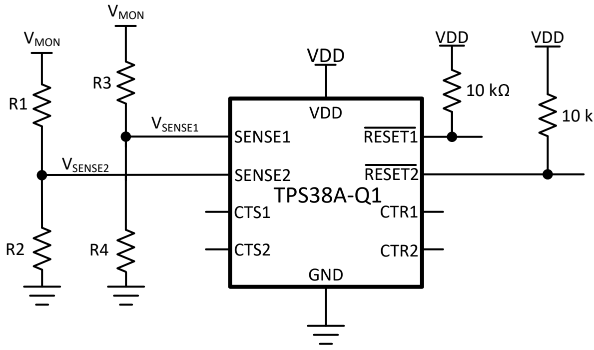


図 9-1. Adjustable Voltage Threshold with External Resistor Dividers

9.2 Application Information

The following sections describe in detail how to properly use this device, depending on the requirements of the final application.

9.3 Typical Application

9.3.1 Design 1: Automotive Off-Battery Monitoring

The initial power stage in automotive applications starts with the 12 V battery. Variation of the battery voltage is common between 9 V and 16 V. Furthermore, if cold-cranking and load dump conditions are considered, voltage transients can occur as low as 3 V and as high as 42 V. In this design example, we are highlighting the ability for low power, direct off-battery voltage supervision. 図 9-2 illustrates an example of how the TPS38-Q1 is monitoring the battery voltage while being powered by it as well. For more information, read this *application report* on how to achieve low I_Q voltage supervision in automotive, wide-V_{IN} applications.

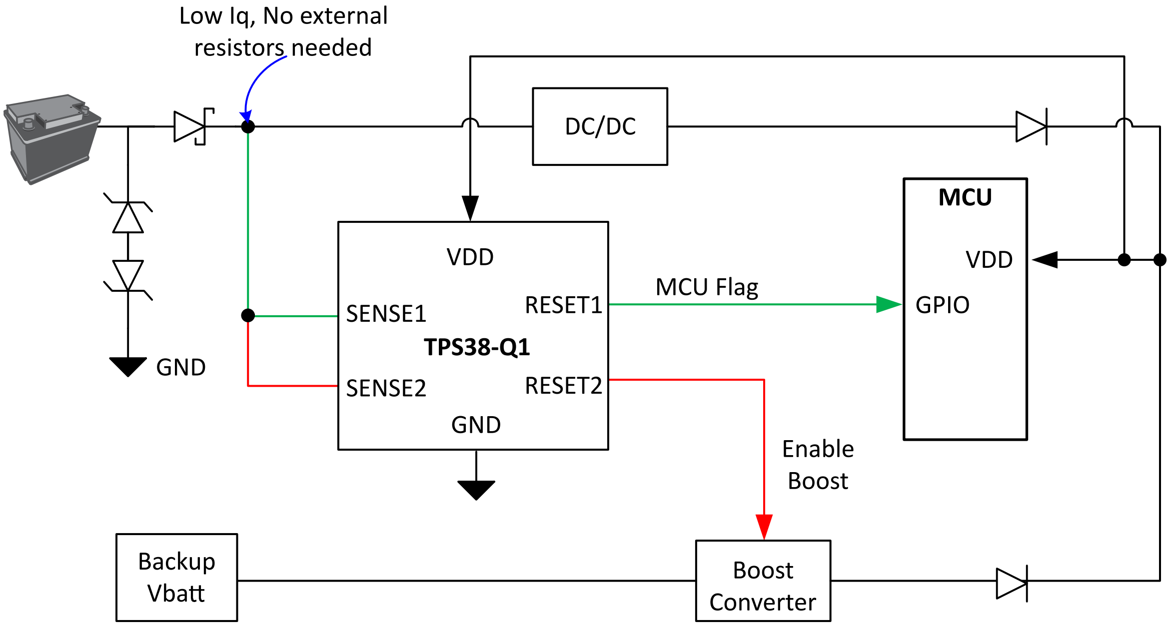


図 9-2. Fast Start Supervisor with Direct Off-Battery Monitoring

9.3.1.1 Design Requirements

This design requires voltage supervision on a 12-V power supply voltage rail with possibility of the 12-V rail rising up as high as 42 V. The undervoltage fault occurs when the power supply voltage drops below 7.7 V.

PARAMETER	DESIGN REQUIREMENT	DESIGN RESULT
Power Rail Voltage Supervision	Monitor 12 V power supply for undervoltage condition, trigger a undervoltage fault at 7.7 V.	TPS38-Q1 provides voltage monitoring with 1.5% max accuracy with adjustable/non-adjustable variations.
Maximum Input Power	Operate with power supply input up to 42 V.	The TPS38-Q1 can support a VDD of up to 65 V.
Output logic voltage	Open-Drain Output Topology	An open-drain output is recommended to provide the correct reset signal, but a push-pull can also be used.
Maximum system current consumption	2 µA max when power supply is at 12 V typical	TPS38-Q1 allows for I_Q to remain low with support of up to 65 V. This allows for no external resistor divider to be required.
Voltage Monitor Accuracy	Maximum voltage monitor accuracy of 1.5%.	The TPS38-Q1 has 1.5% maximum voltage monitor accuracy.
Delay when returning from fault condition	$\overline{\text{RESET}}$ delay of at least 420 ms when returning from a undervoltage fault.	C_{CTR} = 0.33 µF sets 422 ms delay

9.3.1.2 Detailed Design Procedure

The primary advantage of this application is being able to directly monitor a voltage on an automotive battery without needing external resistor dividers on the SENSEx inputs. This keeps the overall I_Q of the design low while still achieving the desired rail monitoring.

As shown in 図 9-2, rail monitoring is done by connecting SENSE1 and SENSE2 inputs directly to the battery rail after the TVS protection diodes. The TPS38-Q1 that is being used in this example is a fixed voltage variant where SENSE1 and SENSE 2 threshold voltages have been set internally by the factory. Word of caution, the TVS protection diodes must be chosen such that the transient voltages on the monitored rails do not exceed the absolute max limit listed in セクション 7.1.

To use this configuration, the specific voltage threshold variation of the device must be chosen according to the application. In this configuration, the '77' variation must be chosen for 7.7 V as shown in 表 10-1.

The device being able to handle 65 V on VDD means the monitored voltage rail can go as high as 42 V for the application transients and not violate the recommended maximum for the supervisor as it usually would. This is useful when monitoring a voltage rail that has a wide range that may go much higher than the nominal rail voltage such as in this case. Good design practice recommends using a 0.1 µF capacitor on the VDD pin and this capacitance may need to increase if using an adjustable version with a resistor divider.

9.3.1.3 Application Curves

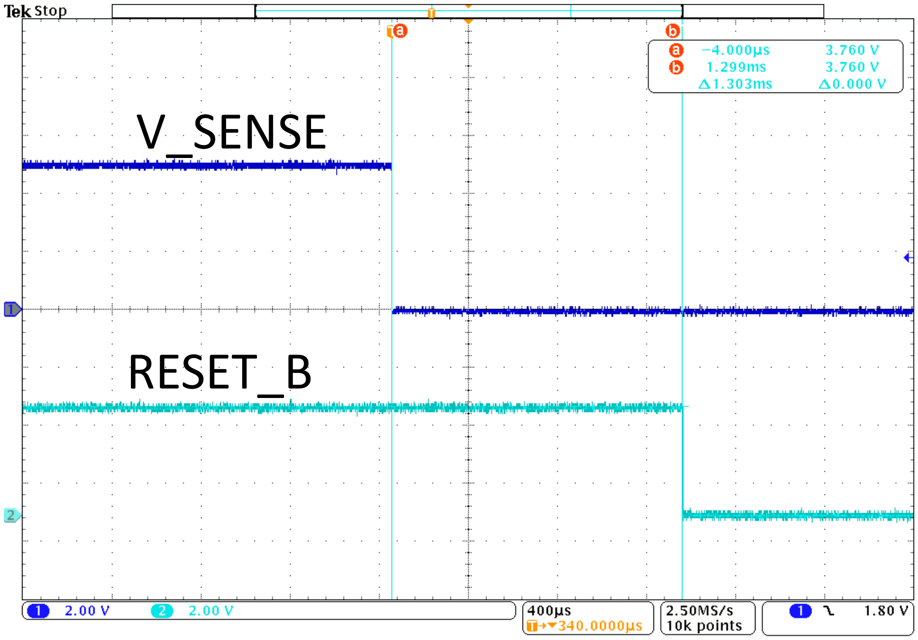


図 9-3. Undervoltage Reset Waveform

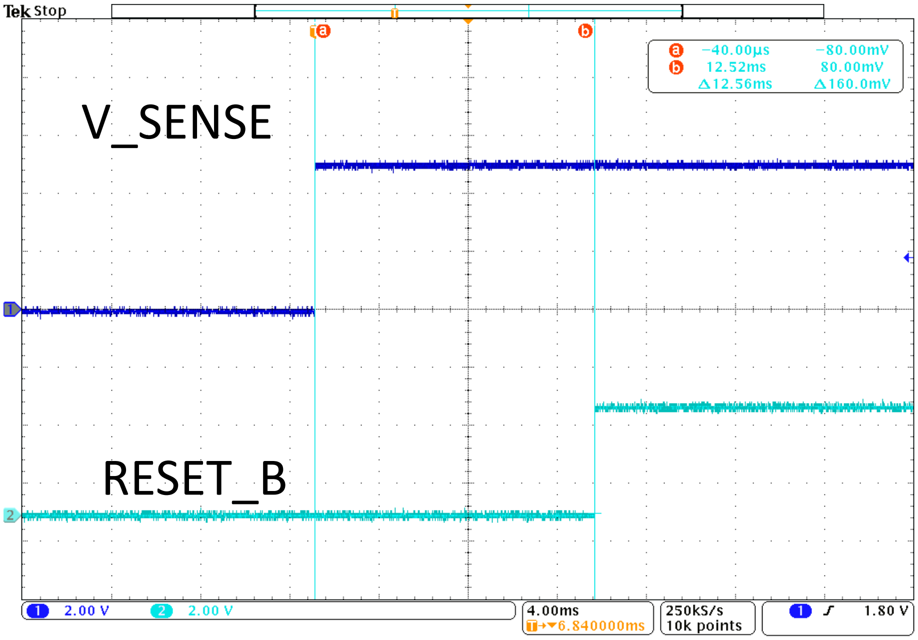


図 9-4. Undervoltage Recovery Waveform

9.4 Power Supply Recommendations

These devices are designed to operate from an input supply with a voltage range between 1.4 V (V_{POR}) to 65 V (max operation). Good analog design practice recommends placing a minimum 0.1 µF ceramic capacitor as near as possible to the VDD pin.

9.4.1 Power Dissipation and Device Operation

The permissible power dissipation for any package is a measure of the capability of the device to pass heat from the power source, the junctions of the IC, to the ultimate heat sink, the ambient environment. Thus, the power dissipation is dependent on the ambient temperature and the thermal resistance across the various interfaces between the die junction and ambient air.

The maximum continuous allowable power dissipation for the device in a given package can be calculated using 式 17:

$$P_{D\text{-}MAX} = ((T_{J\text{-}MAX} - T_A) / R_{\theta JA}) \tag{17}$$

The actual power being dissipated in the device can be represented by 式 18:

$$P_D = V_{DD} \times I_{DD} + p_{RESET} \tag{18}$$

p_{RESET} is calculated by 式 19 or 式 20

$$p_{RESET\ (PUSHPULL)} = VDD - V_{RESET} \times I_{RESET} \tag{19}$$

$$p_{RESET\ (OPEN\text{-}DRAIN)} = V_{RESET} \times I_{RESET} \tag{20}$$

式 17 and 式 18 establish the relationship between the maximum power dissipation allowed due to thermal consideration, the voltage drop across the device, and the continuous current capability of the device. These two equations should be used to determine the optimum operating conditions for the device in the application.

In applications where lower power dissipation (P_D) and/or excellent package thermal resistance ($R_{\theta JA}$) is present, the maximum ambient temperature ($T_{A\text{-}MAX}$) may be increased.

In applications where high power dissipation and/or poor package thermal resistance is present, the maximum ambient temperature ($T_{A\text{-}MAX}$) may have to be de-rated. $T_{A\text{-}MAX}$ is dependent on the maximum operating junction temperature ($T_{J\text{-}MAX\text{-}OP}$ = 125°C), the maximum allowable power dissipation in the device package in the application ($P_{D\text{-}MAX}$), and the junction-to ambient thermal resistance of the part/package in the application ($R_{\theta JA}$), as given by 式 21:

$$T_{A\text{-}MAX} = (T_{J\text{-}MAX\text{-}OP} - (R_{\theta JA} \times P_{D\text{-}MAX})) \tag{21}$$

9.5 Layout

9.5.1 Layout Guidelines

- Make sure that the connection to the VDD pin is low impedance. Good analog design practice is to place a greater than 0.1 µF ceramic capacitor as near as possible to the VDD pin.
- To further improve the noise immunity on the SENSEx pins, placing a 1 nF to 10 nF capacitor between the SENSEx pins and GND can reduce the sensitivity to transient voltages on the monitored signal.
- If a capacitor is used on CTS1, CTS2, CTR1, or CTR2, place these components as close as possible to the respective pins. If the capacitor adjustable pins are left unconnected, make sure to minimize the amount of parasitic capacitance on the pins to less than 5 pF.
- For open-drain variants, place the pull-up resistors on $\overline{\text{RESET1}}$ and $\overline{\text{RESET2}}$ pins as close to the pins as possible.
- When laying out metal traces, separate high voltage traces from low voltage traces as much as possible. If high and low voltage traces need to run close by, spacing between traces should be greater than 20 mils (0.5 mm).
- Do not have high voltage metal pads or traces closer than 20 mils (0.5 mm) to the low voltage metal pads or traces.

9.5.2 Layout Example

The DSK layout example in 図 9-5 shows how the TPS38-Q1 is laid out on a printed circuit board (PCB) with user-defined delays.

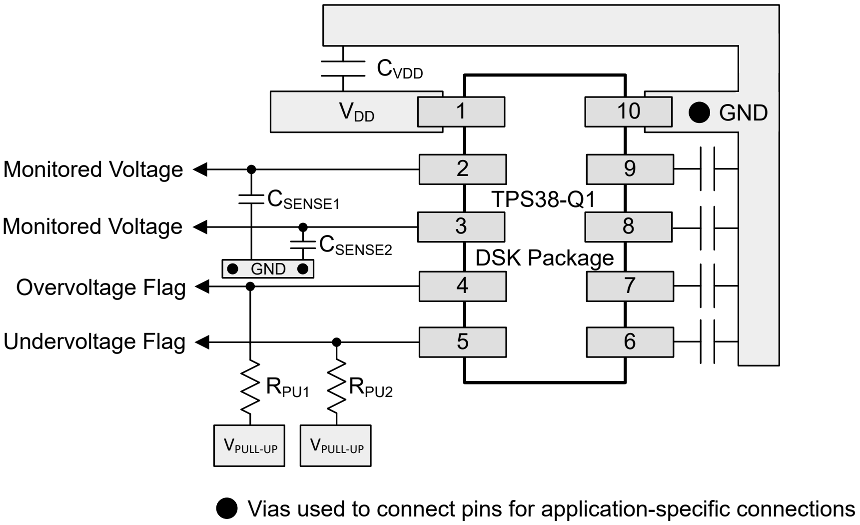
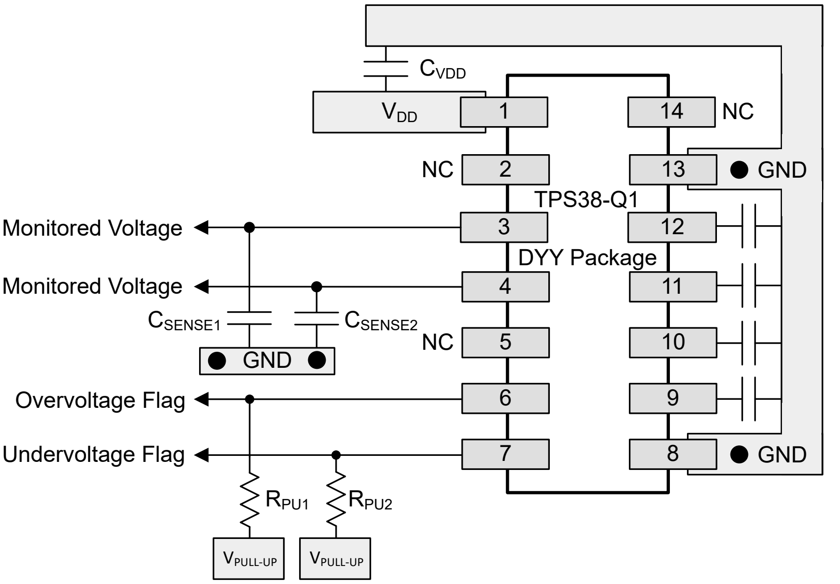


図 9-5. TPS38-Q1 DSK Package Recommended Layout

The DYY layout example in 図 9-6 shows how the TPS38-Q1 is laid out on a printed circuit board (PCB) with user-defined delays.



● Vias used to connect pins for application-specific connections

図 9-6. TPS38-Q1 DYY Package Recommended Layout

9.5.3 Creepage Distance

Per IEC 60664 Creepage is the shortest distance between two conductive parts or as shown in 図 9-7 the distance between high voltage conductive parts and grounded parts, the floating conductive part is ignored and subtracted from the total distance.

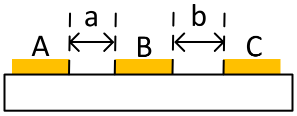


図 9-7. Creepage Distance

図 9-7 details:

- A = Left pins (high voltage)
- B = Central pad (not internally connected, can be left floating or connected to GND)
- C = Right pins (low voltage)
- Creepage distance = a + b

10 Device and Documentation Support

10.1 Device Nomenclature

セクション 5 shows how to decode the function of the device based on its part number

表 10-1 shows TPS38-Q1 possible voltage options per channel. Contact TI sales representatives or on TI's E2E forum for details and availability of other options; minimum order quantities apply.

表 10-1. Voltage Options

100 mV STEPS				400 mV STEPS		500 mV STEPS		1 V STEPS	
NOMEN-CLATURE	VOLTAGE OPTIONS	NOMEN-CLATURE	VOLTAGE OPTIONS	NOMEN-CLATURE	VOLTAGE OPTIONS	NOMEN-CLATURE	VOLTAGE OPTIONS	NOMEN-CLATURE	VOLTAGE OPTIONS
01	800 mV (divider bypass)	**70**	7.0 V	**A0**	10.4 V	**D0**	20.5 V	**F0**	31.0 V
27	2.7 V	**71**	7.1 V	**A1**	10.8 V	**D1**	21.0 V	**F1**	32.0 V
28	2.8 V	**72**	7.2 V	**A2**	11.2 V	**D2**	21.5 V	**F2**	33.0 V
29	2.9 V	**73**	7.3 V	**A3**	11.6 V	**D3**	22.0 V	**F3**	34.0 V
30	3.0 V	**74**	7.4 V	**A4**	12.0 V	**D4**	22.5 V	**F4**	35.0 V
31	3.1 V	**75**	7.5 V	**A5**	12.4 V	**D5**	23.0 V	**F5**	36.0 V
32	3.2 V	**76**	7.6 V	**A6**	12.8 V	**D6**	23.5 V		
33	3.3 V	**77**	7.7 V	**A7**	13.2 V	**D7**	24.0 V		
34	3.4 V	**78**	7.8 V	**A8**	13.6 V	**D8**	24.5 V		
35	3.5 V	**79**	7.9 V	**A9**	14.0 V	**D9**	25.0 V		
36	3.6 V	**80**	8.0 V	**B0**	14.4 V	**E0**	25.5 V		
37	3.7 V	**81**	8.1 V	**B1**	14.8 V	**E1**	26.0 V		
38	3.8 V	**82**	8.2 V	**B2**	15.2 V	**E2**	26.5 V		
39	3.9 V	**83**	8.3 V	**B3**	15.6 V	**E3**	27.0 V		
40	4.0 V	**84**	8.4 V	**B4**	16.0 V	**E4**	27.5 V		
41	4.1 V	**85**	8.5 V	**B5**	16.4 V	**E5**	28.0 V		
42	4.2 V	**86**	8.6 V	**B6**	16.8 V	**E6**	28.5 V		
43	4.3 V	**87**	8.7 V	**B7**	17.2 V	**E7**	29.0 V		
44	4.4 V	**88**	8.8 V	**B8**	17.6 V	**E8**	29.5 V		
45	4.5 V	**89**	8.9 V	**B9**	18.0 V	**E9**	30.0 V		
46	4.6 V	**90**	9.0 V	**C0**	18.4 V				
47	4.7 V	**91**	9.1 V	**C1**	18.8 V				
48	4.8 V	**92**	9.2 V	**C2**	19.2 V				
49	4.9 V	**93**	9.3 V	**C3**	19.6 V				
50	5.0 V	**94**	9.4 V	**C4**	20.0 V				
51	5.1 V	**95**	9.5 V						
52	5.2 V	**96**	9.6 V						
53	5.3 V	**97**	9.7 V						
54	5.4 V	**98**	9.8 V						
55	5.5 V	**99**	9.9 V						
56	5.6 V	**00**	10.0 V						
57	5.7 V								
58	5.8 V								
59	5.9 V								
60	6.0 V								

表 10-1. Voltage Options (continued)

100 mV STEPS				400 mV STEPS		500 mV STEPS		1 V STEPS	
NOMENCLATURE	VOLTAGE OPTIONS	NOMENCLATURE	VOLTAGE OPTIONS	NOMENCLATURE	VOLTAGE OPTIONS	NOMENCLATURE	VOLTAGE OPTIONS	NOMENCLATURE	VOLTAGE OPTIONS
61	6.1 V								
62	6.2 V								
63	6.3 V								
64	6.4 V								
65	6.5 V								
66	6.6 V								
67	6.7 V								
68	6.8 V								
69	6.9 V								

10.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、ti.com のデバイス製品フォルダを開いてください。「更新の通知を受け取る」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

10.3 サポート・リソース

TI E2E™ サポート・フォーラムは、エンジニアが検証済みの回答と設計に関するヒントをエキスパートから迅速かつ直接得ることができる場所です。既存の回答を検索したり、独自の質問をしたりすることで、設計で必要な支援を迅速に得ることができます。

リンクされているコンテンツは、該当する貢献者により、現状のまま提供されるものです。これらは TI の仕様を構成するものではなく、必ずしも TI の見解を反映したものではありません。TI の使用条件を参照してください。

10.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.
すべての商標は、それぞれの所有者に帰属します。

10.5 静電気放電に関する注意事項

この IC は、ESD によって破損する可能性があります。テキサス・インスツルメンツは、IC を取り扱う際には常に適切な注意を払うことを推奨します。正しい取り扱いおよび設置手順に従わない場合、デバイスを破損するおそれがあります。

ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

10.6 用語集

テキサス・インスツルメンツ用語集	この用語集には、用語や略語の一覧および定義が記載されています。

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TPS38A010122DSKRQ1	Active	Production	SON (DSK) | 10	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2KJL
TPS38A010122DSKRQ1.A	Active	Production	SON (DSK) | 10	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2KJL
TPS38A0101DDDSKRQ1	Active	Production	SON (DSK) | 10	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	32GL
TPS38A0101DDDSKRQ1.A	Active	Production	SON (DSK) | 10	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	32GL
TPS38A5151IIDYYRQ1	Active	Production	SOT-23-THIN (DYY) | 14	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	38A5151IIQ
TPS38A5151IIDYYRQ1.A	Active	Production	SOT-23-THIN (DYY) | 14	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	38A5151IIQ
TPS38A950122DSKRQ1	Active	Production	SON (DSK) | 10	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	32KL
TPS38A950122DSKRQ1.A	Active	Production	SON (DSK) | 10	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	32KL
TPS38AB9B9AADYYRQ1	Active	Production	SOT-23-THIN (DYY) | 14	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	38AB9B9AQ
TPS38B4848EEDSKRQ1	Active	Production	SON (DSK) | 10	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2KCL
TPS38B4848EEDSKRQ1.A	Active	Production	SON (DSK) | 10	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2KCL
TPS38B5858FFDSKRQ1	Active	Production	SON (DSK) | 10	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2KBL
TPS38B5858FFDSKRQ1.A	Active	Production	SON (DSK) | 10	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2KBL
TPS38G6363HHDSKRQ1	Active	Production	SON (DSK) | 10	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-	45AL
TPS38J010122DSKRQ1	Active	Production	SON (DSK) | 10	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	32IL
TPS38J010122DSKRQ1.A	Active	Production	SON (DSK) | 10	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	32IL
TPS38J010155DSKRQ1	Active	Production	SON (DSK) | 10	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2KEL
TPS38J010155DSKRQ1.A	Active	Production	SON (DSK) | 10	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2KEL

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

[4] **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

[5] **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

[6] **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF TPS38-Q1 :

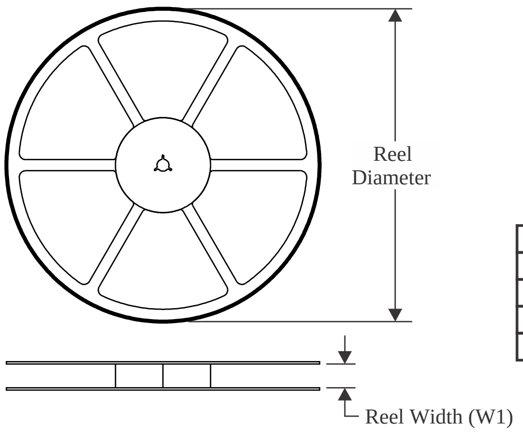
- Catalog : TPS38

NOTE: Qualified Version Definitions:

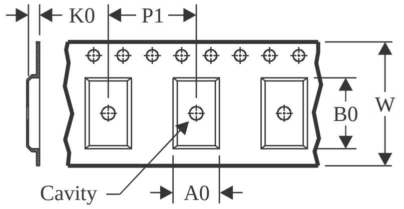
  - Catalog - TI's standard catalog product

TAPE AND REEL INFORMATION

REEL DIMENSIONS

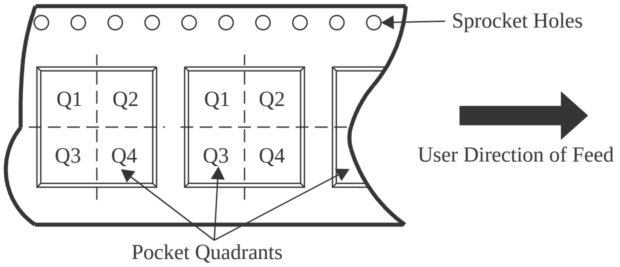


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

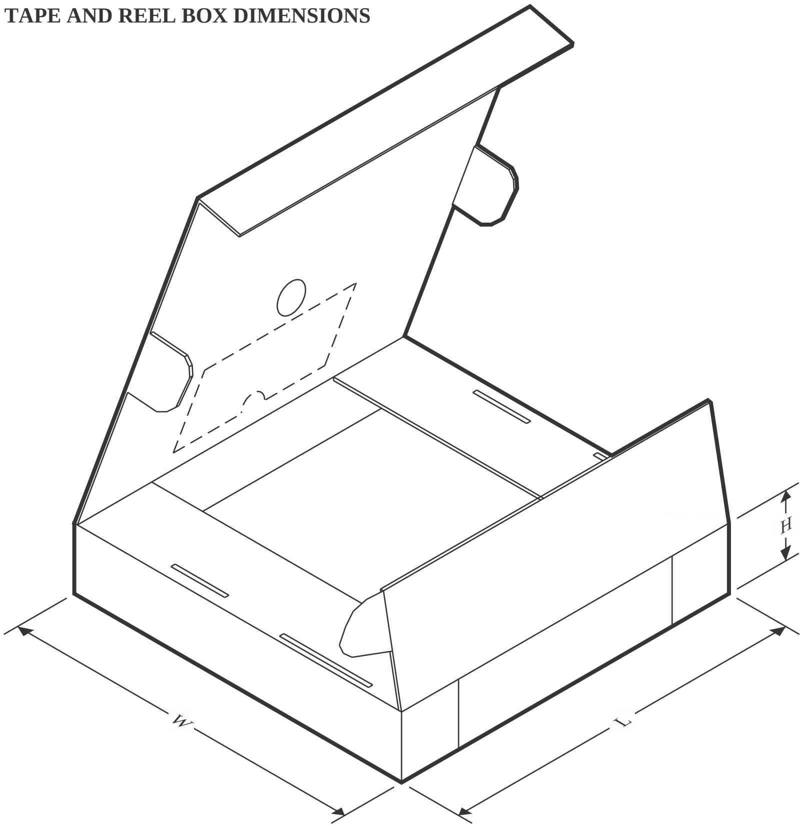
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS38A010122DSKRQ1	SON	DSK	10	3000	180.0	8.4	2.8	2.8	1.0	4.0	8.0	Q2
TPS38A0101DDDSKRQ1	SON	DSK	10	3000	180.0	8.4	2.8	2.8	1.0	4.0	8.0	Q2
TPS38A5151IIDYYRQ1	SOT-23-THIN	DYY	14	3000	330.0	12.4	4.8	3.6	1.6	8.0	12.0	Q3
TPS38A950122DSKRQ1	SON	DSK	10	3000	180.0	8.4	2.8	2.8	1.0	4.0	8.0	Q2
TPS38AB9B9AADYYRQ1	SOT-23-THIN	DYY	14	3000	330.0	12.4	4.8	3.6	1.6	8.0	12.0	Q3
TPS38B4848EEDSKRQ1	SON	DSK	10	3000	180.0	8.4	2.8	2.8	1.0	4.0	8.0	Q2
TPS38B5858FFDSKRQ1	SON	DSK	10	3000	180.0	8.4	2.8	2.8	1.0	4.0	8.0	Q2
TPS38G6363HHDSKRQ1	SON	DSK	10	3000	180.0	8.4	2.8	2.8	1.0	4.0	8.0	Q2
TPS38J010122DSKRQ1	SON	DSK	10	3000	180.0	8.4	2.8	2.8	1.0	4.0	8.0	Q2
TPS38J010155DSKRQ1	SON	DSK	10	3000	180.0	8.4	2.8	2.8	1.0	4.0	8.0	Q2

TAPE AND REEL BOX DIMENSIONS



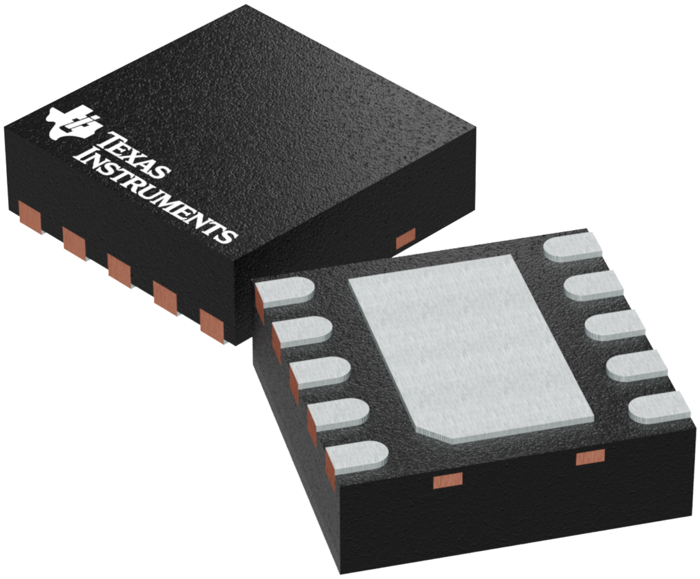
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS38A010122DSKRQ1	SON	DSK	10	3000	210.0	185.0	35.0
TPS38A0101DDDSKRQ1	SON	DSK	10	3000	210.0	185.0	35.0
TPS38A5151IIDYYRQ1	SOT-23-THIN	DYY	14	3000	336.6	336.6	31.8
TPS38A950122DSKRQ1	SON	DSK	10	3000	210.0	185.0	35.0
TPS38AB9B9AADYYRQ1	SOT-23-THIN	DYY	14	3000	336.6	336.6	31.8
TPS38B4848EEDSKRQ1	SON	DSK	10	3000	210.0	185.0	35.0
TPS38B5858FFDSKRQ1	SON	DSK	10	3000	210.0	185.0	35.0
TPS38G6363HHDSKRQ1	SON	DSK	10	3000	210.0	185.0	35.0
TPS38J010122DSKRQ1	SON	DSK	10	3000	210.0	185.0	35.0
TPS38J010155DSKRQ1	SON	DSK	10	3000	210.0	185.0	35.0

DSK 10 **WSON - 0.8 mm max height**

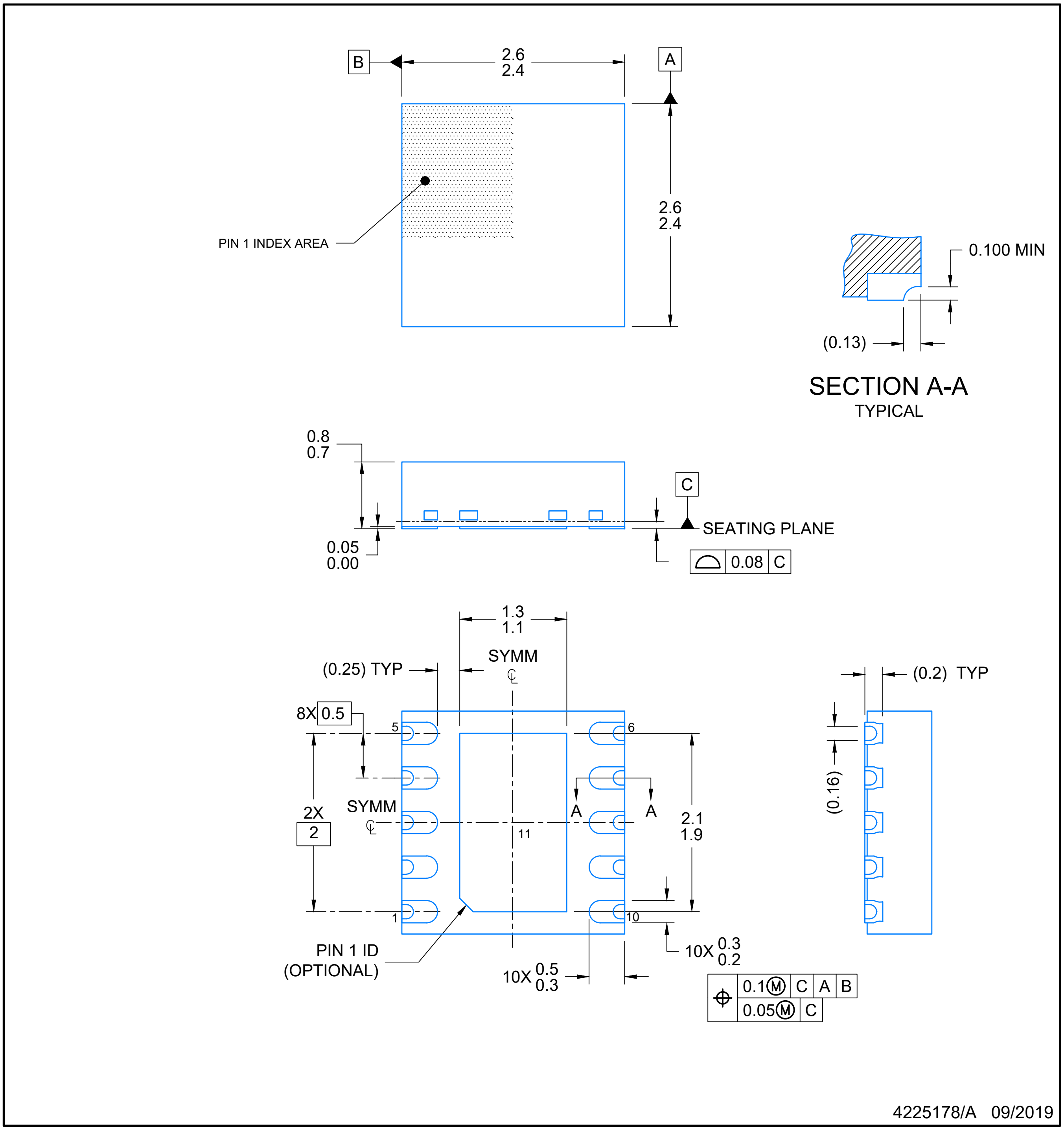
2.5 x 2.5 mm, 0.5 mm pitch

PLASTIC SMALL OUTLINE - NO LEAD



Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

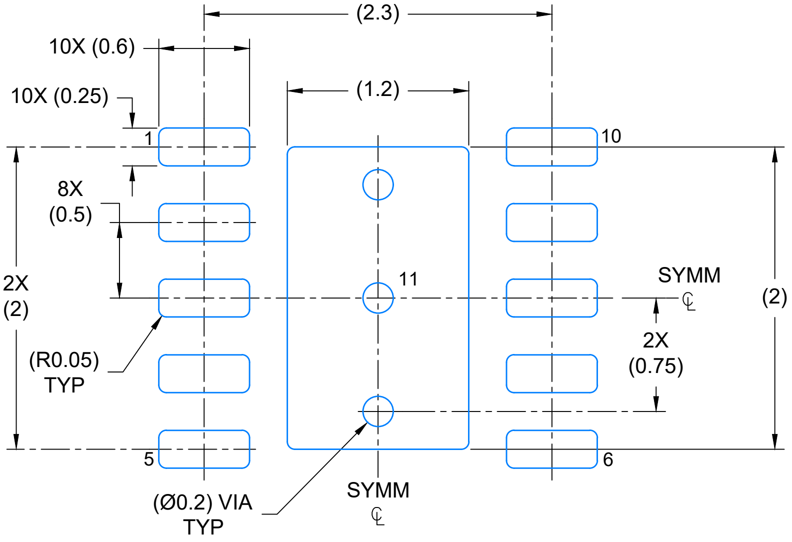
4225304/A



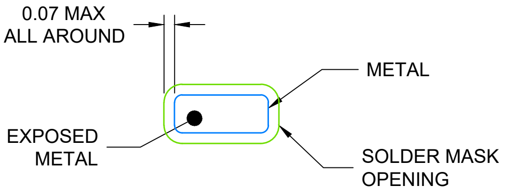
4225178/A 09/2019

NOTES:

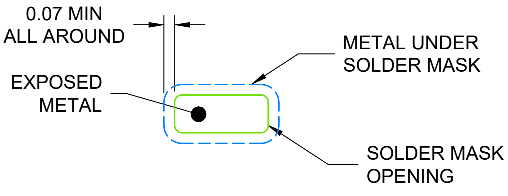
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X



NON SOLDER MASK
DEFINED
(PREFERRED)



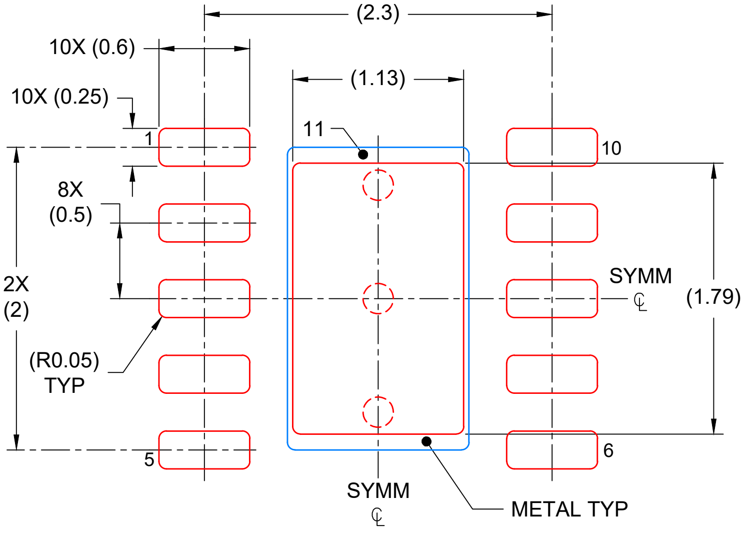
SOLDER MASK
DEFINED

SOLDER MASK DETAILS

4225178/A 09/2019

NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

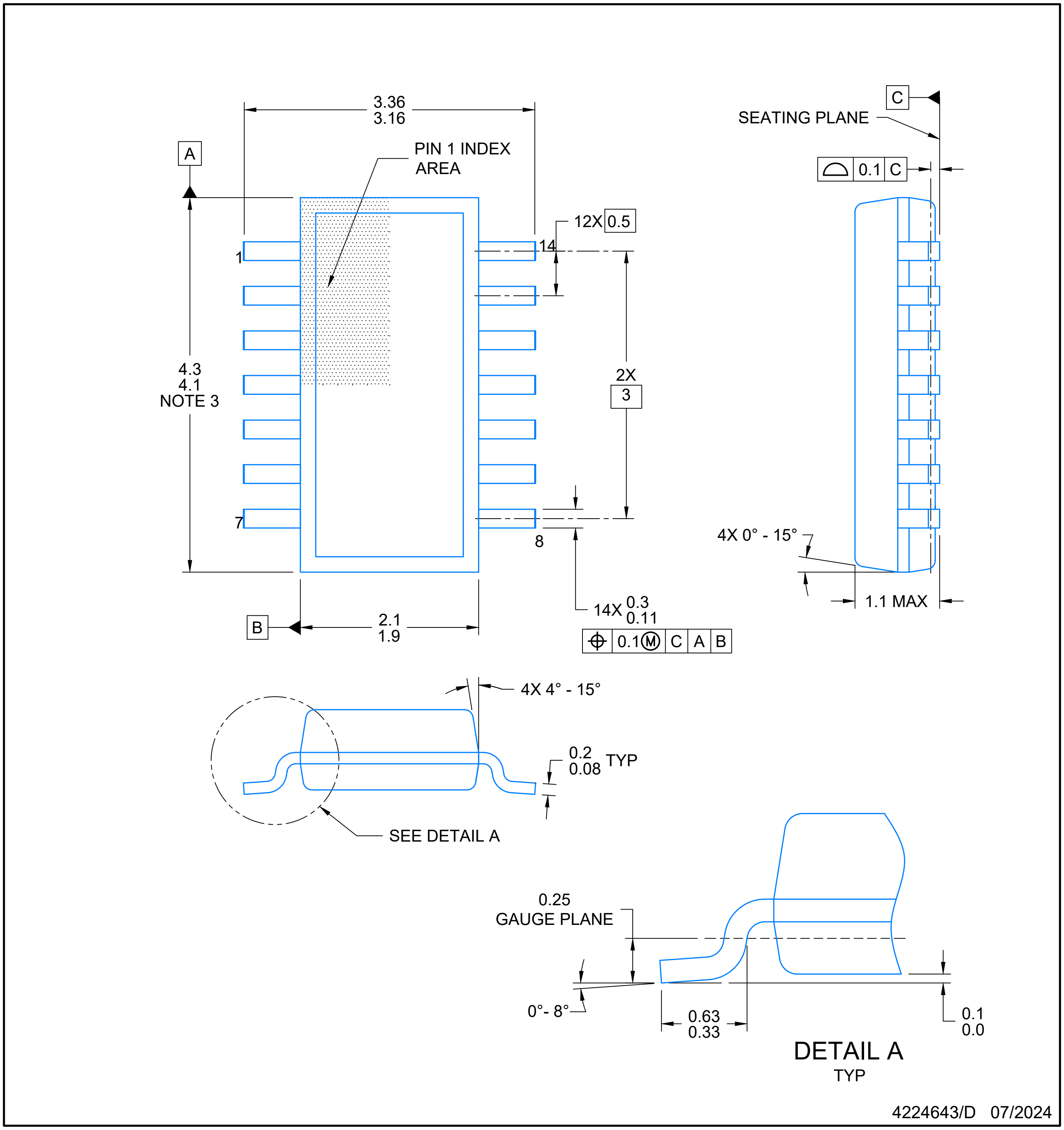


SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD
84% PRINTED COVERAGE BY AREA
SCALE: 20X

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



4224643/D 07/2024

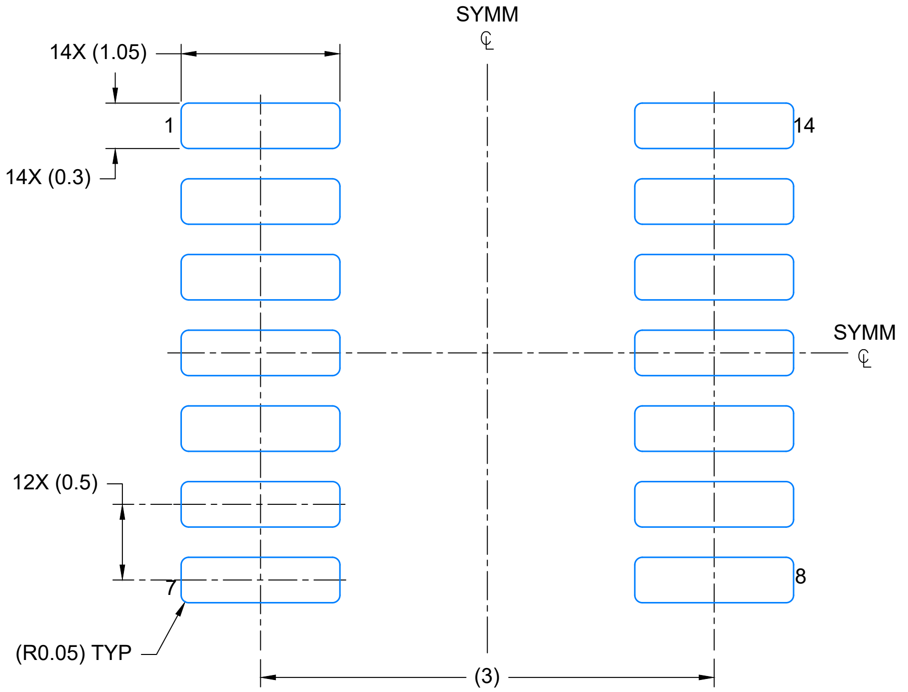
NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
5. Reference JEDEC Registration MO-345, Variation AB

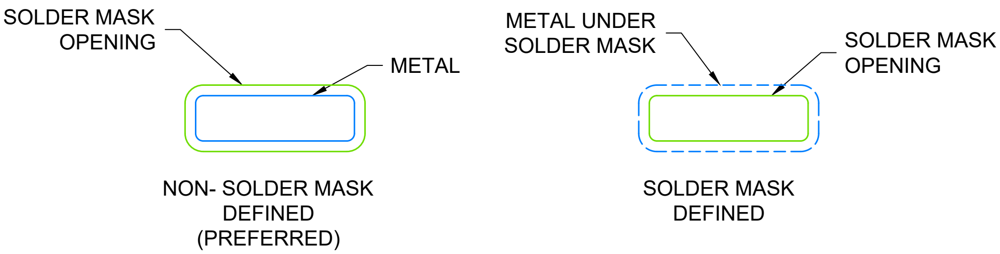
EXAMPLE BOARD LAYOUT

SOT-23-THIN - 1.1 mm max height

PLASTIC SMALL OUTLINE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X

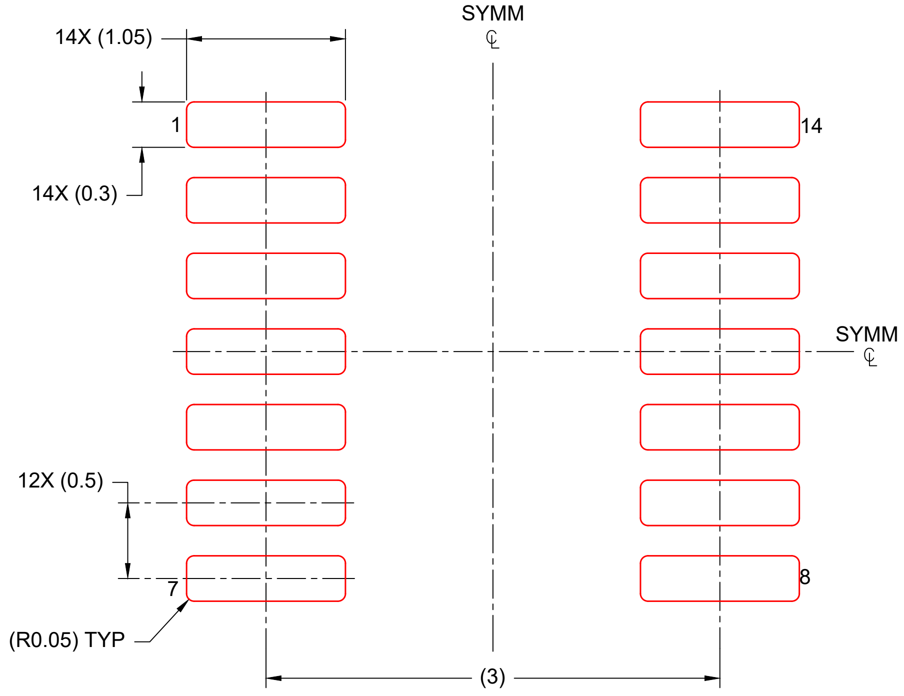


SOLDER MASK DETAILS

4224643/D 07/2024

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 20X

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

重要なお知らせと免責事項

最終更新日：2025 年 10 月